

# Detectors for sLHC

**G. Casse**

**University of Liverpool Group**

**6<sup>th</sup> December 2007**

- **Proposed Tracker Layout and Simulations (Radiation and Occupancy)**
- **Sensor and FE Electronics R&D**
- **Microstrip Module and Engineering Concepts**
- **Power, DCS, Opto-electronics, Services, Cooling, ...**
- **Conclusions**

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# *The European strategy for particle physics*

<http://council-strategygroup.web.cern.ch/council-strategygroup/>

“The LHC will be the energy frontier machine for the foreseeable future, maintaining European leadership in the field; *the highest priority is to fully exploit the physics potential of the LHC, resources for completion of the initial programme have to be secured such that machine and experiments can operate optimally at their design performance.* A subsequent major luminosity upgrade (SLHC), motivated by physics results and operation experience, will be enabled by focussed R&D; *to this end, R&D for machine and detectors has to be vigorously pursued now and centrally organized towards a luminosity upgrade by around 2015.”*

# Why Discuss Upgrading the LHC Already?

Because we have to start the R&D now

## Trigger Electronics:

- Most front-end electronics can probably stay but need faster clock speed and deeper pipelines
- Extensions to trigger capability required
- Need to maintain L1 output rate (more data per event)
  - Must upgrade detector backend electronics
    - increase bandwidth to deal with more data per event
  - Modify trigger algorithms to deal with high occupancy (and increase thresholds)

## L-Ar:

- Performance degradation due to high rates in EndCap.  
(High ionisation gives big voltage drops, electronic is inaccessible, L-Ar boiling!)

## TileCal:

- Some radiation damage of scintillators
- Challenging calibration with strong increase in pile-up

## Muon systems:

- Degradation in performance due to high rates, in particular in the forward regions:
  - Will need additional shielding for forward region
  - May need beryllium beampipe
  - Aging/radiation damage needs confirmation for SLHC operation
- Huge expense and disruption if chambers need replacement

## Inner Detector tracking systems:

- **The entire Inner Detector will have to be rebuilt**

# ATLAS Inner Detector Replacement

To keep ATLAS running more than 10 years the inner tracker will have to go ...  
(Current tracker designed to survive up to  $730 \text{ fb}^{-1} \approx 10 \text{ Mrad}$  in strip detectors)

For the luminosity-upgrade the new tracker will have to cope with:

- much higher occupancy levels
- much higher dose rates

To build a new tracker for 2015, major R&D programme already needed.

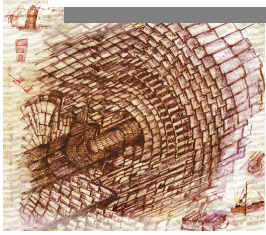
Timescales:

- R&D leading into a full tracker Technical Design Report (TDR) in 2010
- Construction phase to start immediately TDR completed and approved.

The intermediate radius barrels are expected to consist of modules arranged in rows with common cooling, power, clocking and cooling.

The TDR will require prototype super-modules/staves (complete module rows as an integrated structure) to be assembled and fully evaluated

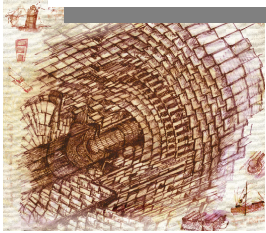
All components will need to demonstrate unprecedented radiation hardness



## The challenge...



- **Build a replacement tracker for  $\mathcal{L} = 10^{35} \text{ cm}^{-2} \cdot \text{s}^{-1}$  with equal or better performance, AND L1 Trigger Capability**
- **To do so, solve several very difficult problems**
  - deliver power - probably requiring greater currents
  - develop sensors to tolerate radiation fluences  $\sim 10x$  larger than LHC
  - construct readout systems which can also contribute to the L1 trigger using tracker data
  - ...and so on...
- **It is probably as difficult a challenge as the original LHC detectors were in 1990**
  - or possibly harder...

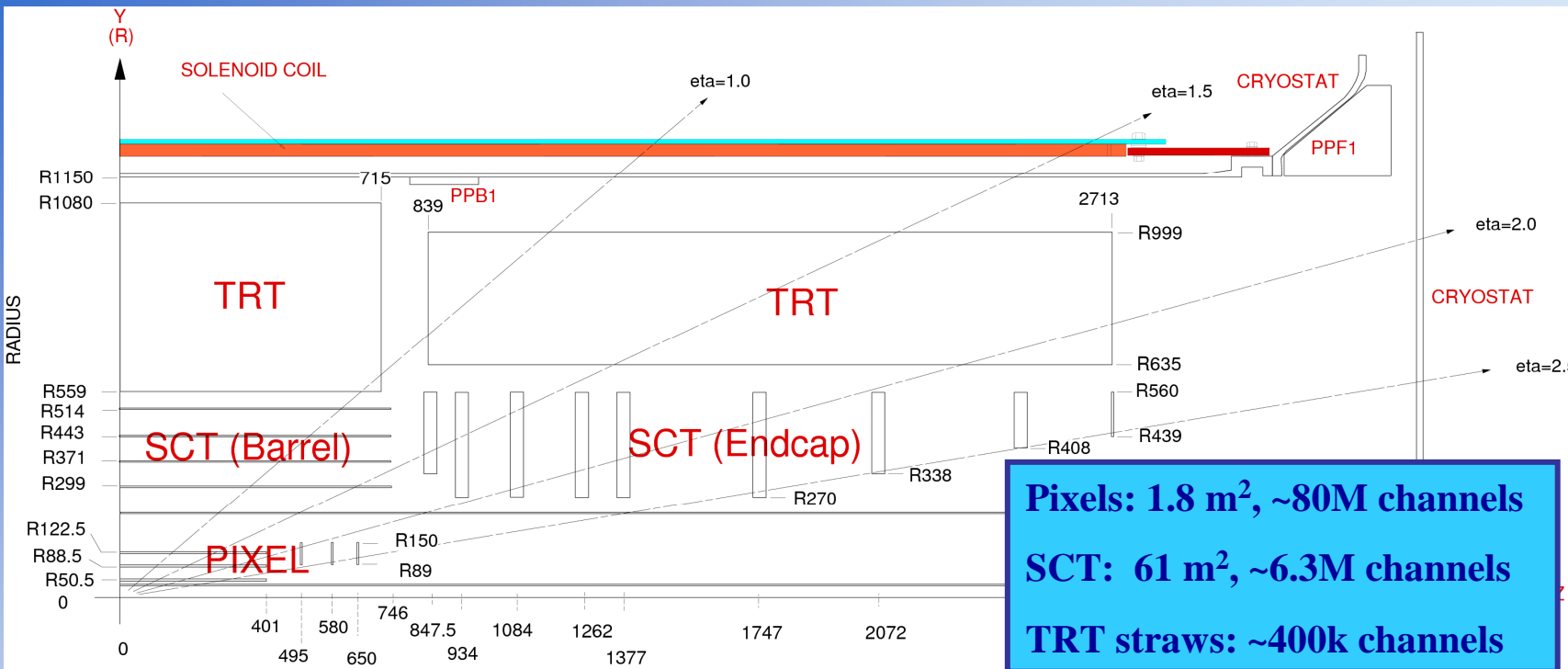


## Planning an Upgrade Project

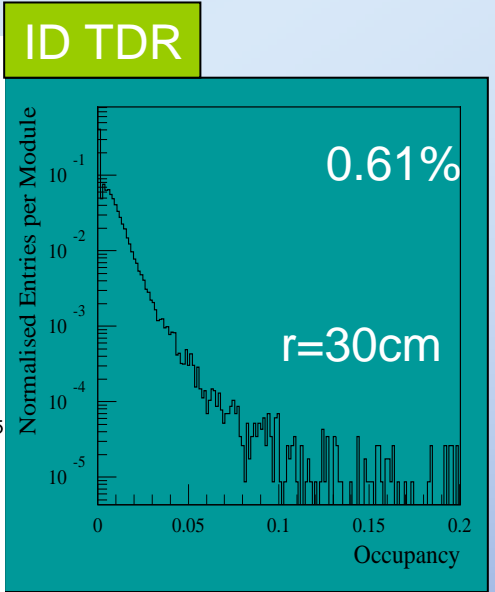


- **To define the project scope we need (to iterate to establish)**
  - ...some idea of timescale
  - ...assessment of resources expected to be available, and those needed
    - Including - importantly- likely effort
    - with time profile
- **Planning assumption: ~10 years - from now - to operational upgraded tracker, with possible breakdown:**
  - 5 years R&D
  - 2 years Qualification
  - 3 years Construction
  - 6 months Installation and Ready for Commissioning
- **NB experience tells us that system approach and attention to QA are important considerations from a very early stage**

# Current ATLAS Inner Tracker Layout



**Pixels: 1.8 m<sup>2</sup>, ~80M channels**  
**SCT: 61 m<sup>2</sup>, ~6.3M channels**  
**TRT straws: ~400k channels**



**Mean Occupancy in Innermost Layer of Current SCT**

**Pixels (50 μm × 400 μm): 3 barrels, 2×3 disks**

- Pattern recognition in high occupancy region
- Impact parameter resolution (in 3d)

Radiation hard technology: n<sup>+</sup>-in-n Silicon technology, operated at -6°C

**Strips (80 μm × 12 cm) (small stereo angle): “SCT” 4 barrels, 2×9 disks**

- pattern recognition
- momentum resolution

p-strips in n-type silicon, operated at -7°C

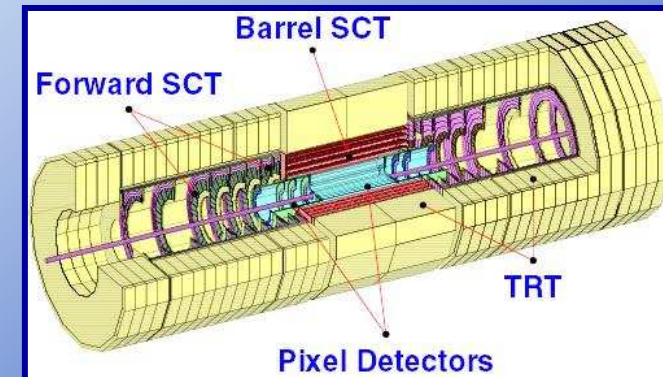
**TRT 4mm diameter straw drift tubes: barrel + wheels**

- Additional pattern recognition by having many hits (~36)
- Standalone electron id. from transition radiation

5cm < r < 15cm

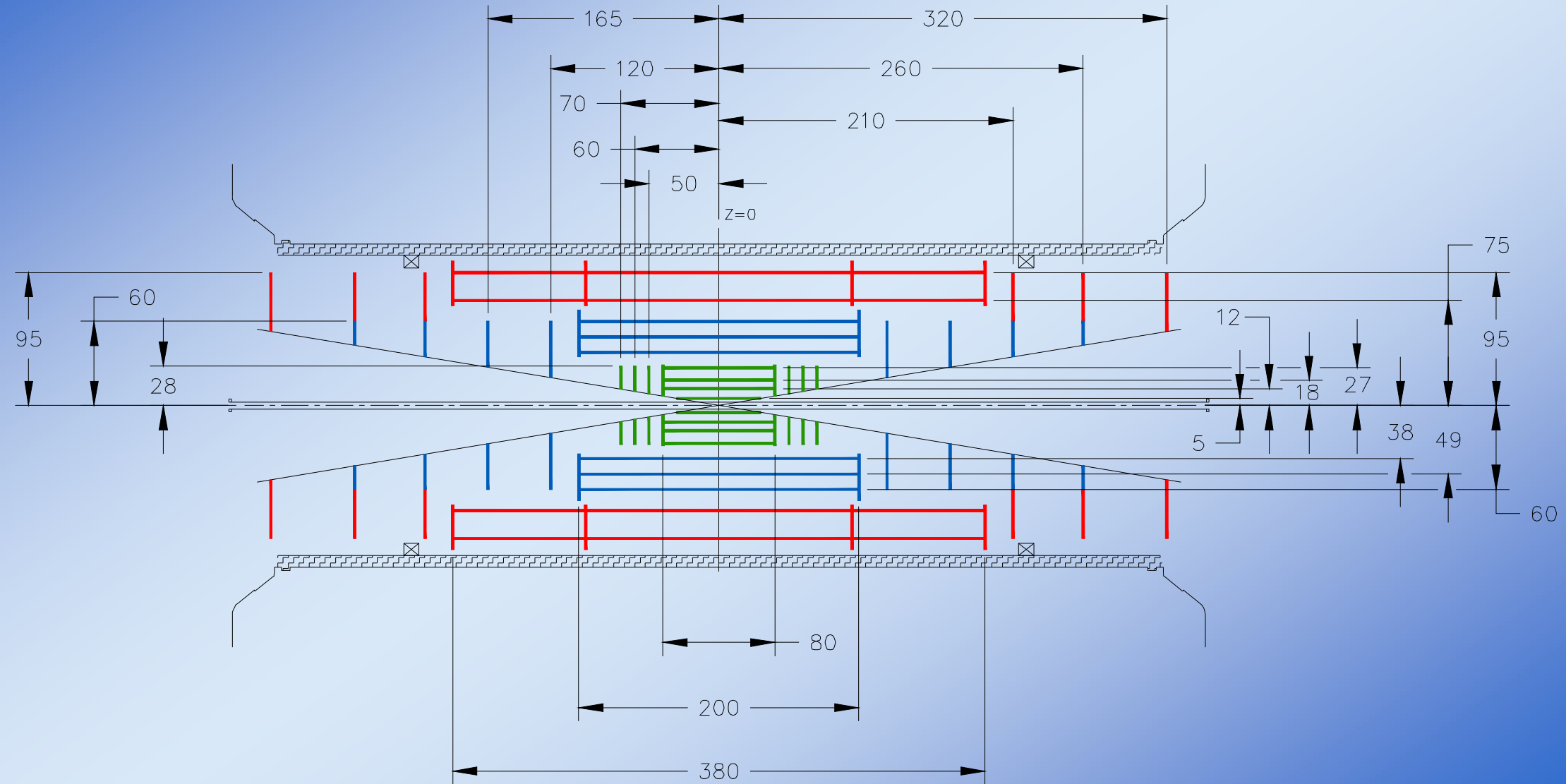
30cm < r < 51cm

55cm < r < 105cm





# Proposed Upgrade Layout

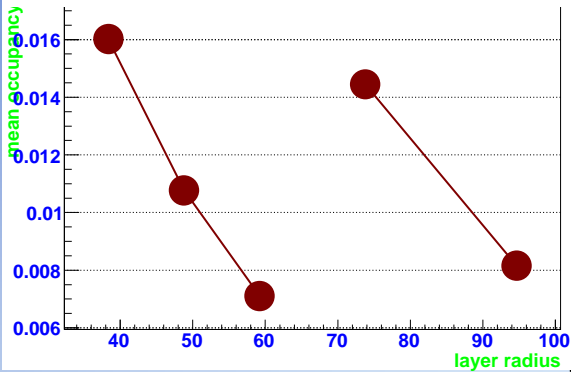


# New SLHC Layout Implications

## Strawman 4+3+2

<b>Pixels:</b>	<b>r=5cm, 12cm, 18cm, 27cm</b>	<b>z=±40cm</b>
<b>Short (2.4 cm) <math>\mu</math>-strips (stereo layers):</b>	<b>r=38cm, 49cm, 60cm</b>	<b>z=±100cm</b>
<b>Long (9.6 cm) <math>\mu</math>-strips (stereo layers):</b>	<b>r=75cm, 95cm</b>	<b>z=±190cm</b>

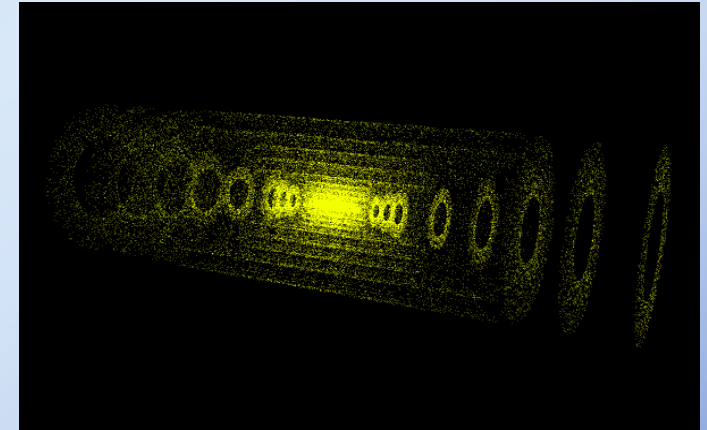
### Short and Long Strip Occupancy



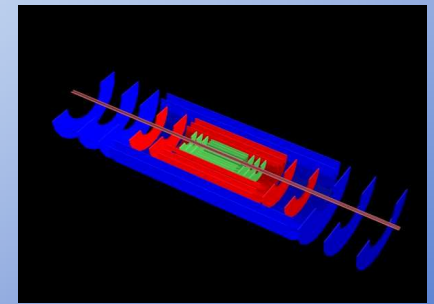
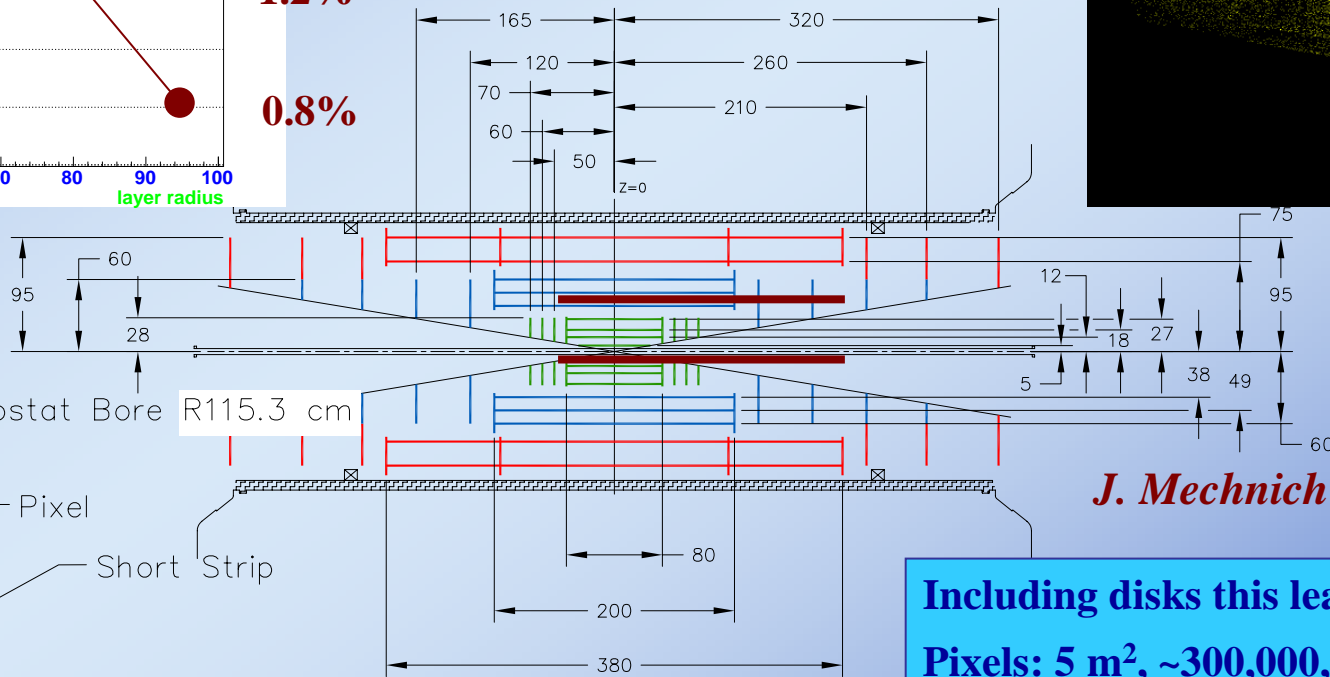
**1.6%** Only LO MC (Pythia) . May need to include  $\times 2$  safety factor?

**1.2%**

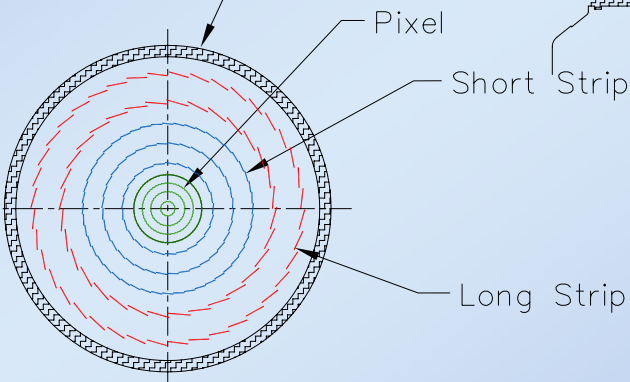
**0.8%**



*J. Tseng*



*J. Mechnich*



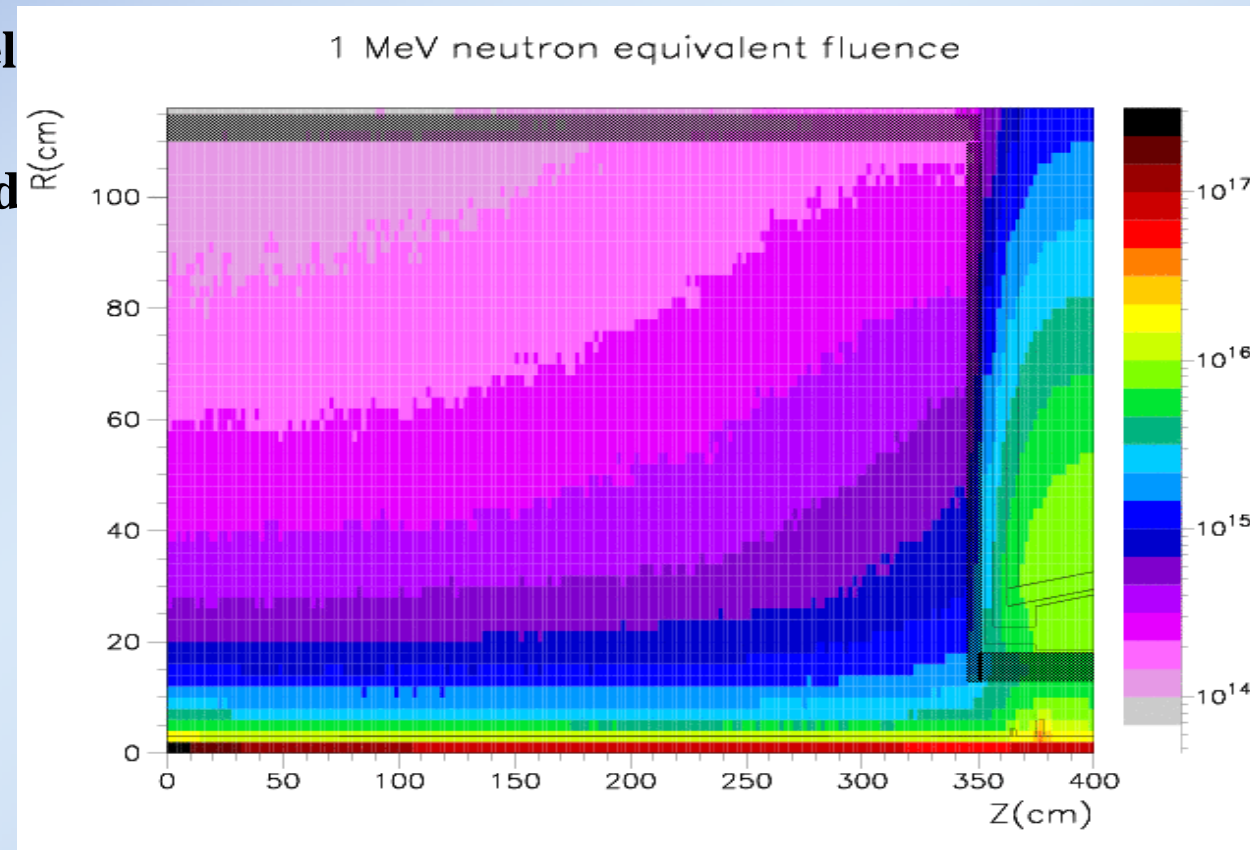
**Including disks this leads to:**

- Pixels:** 5 m<sup>2</sup>, ~300,000,000 channels
- Short strips:** 60 m<sup>2</sup>, ~28,000,000 channels
- Long strips:** 100 m<sup>2</sup>, ~15,000,000 channels

# Radiation Levels

- With safety factor of two, need pixel b-layer to survive up to  $10^{16}n_{eq}/cm^2$
- Short microstrip layers to withstand  $9 \times 10^{14}n_{eq}/cm^2$  (50% neutrons)
- Outer layers up to  $4 \times 10^{14}n_{eq}/cm^2$  (and mostly neutrons)
  - Issues of thermal management and shot noise. Silicon looks to need to be at  $\sim -25^\circ\text{C}$  (depending on details of module design).
  - High levels of activation will require careful consideration for access and maintenance.

Issues of coolant temperature, module design, sensor geometry, radiation length, etc etc all heavily interdependent.



*Quarter slice through ATLAS inner tracker Region, with 5cm moderator lining calorimeters. Fluences obtained using FLUKA2006, assuming an integrated luminosity of  $3000fb^{-1}$ .*

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# B-layer: Replacement → Upgrade

- *ATLAS considers to have a B-layer replacement after ~3 year of integrated full LHC luminosity (2012) and replace completely the Inner Tracker with a fully silicon version for SLHC (2016).*
  
- *The B-layer replacement can be seen as an intermediate step towards the full upgrade. Performance improvements for the detector (here some issues more related to FE chip):*
  - **Reduce radius** → Improve radiation hardness (→ 3D sensors, or possibly, thin planar detectors, diamond, gas, ...?)
  - **Reduce pixel cell size and architecture related dead time** (→ design FE for higher luminosity, use 0.13 μm 8 metal CMOS)
  - **Reduce material budget** of the b-layer (~3%  $X_0$  → 2.0÷2.5%  $X_0$ )
  - **increase the module live fraction** (→ increase chip size, > 12×14 mm<sup>2</sup>) possibly use “active edge” technology for sensor.
  - **Use faster R/O links**, move MCC at the end of stave
  
- *The B-layer for the upgrade will need radiation hardness ( $10^{15} \rightarrow 10^{16} n_{eq}/cm^2$ ) and cope with detector occupancies up to ( $\times 15$ )*

# New Pixel FE-ASIC Design

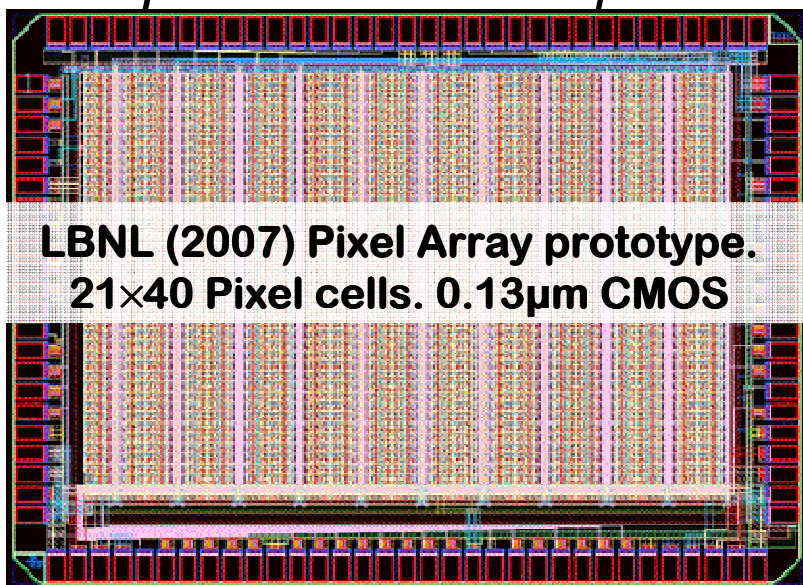


Design of a new Front-End chip (FE-I4) is going on as a Collaborative Work of 5 Laboratories: Bonn, CPPM, Genova, LBNL, Nikhef

## FE-I4 tentative schedule

- 9/2007: Architecture definition
- 10/2007: Footprint frozen
- 01/2008: Initial Design review
- 12/2008: Final Design review

Some prototype silicon made of small blocks and analog part of the pixel cell in 0.13  $\mu\text{m}$ .



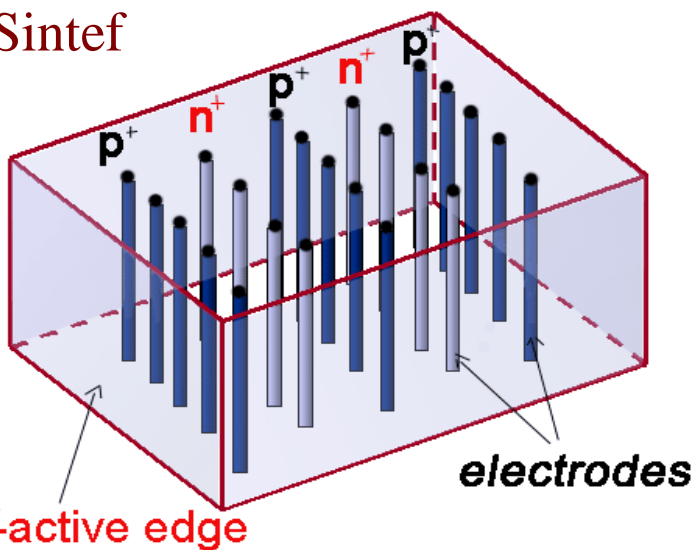
Main Parameter	Value	Unit
Pixel size	50 x 250	$\mu\text{m}^2$
Input	DC-coupled negative polarity	
Normal pixel input capacitance range	300Ö500	fF
In-time threshold with 20ns gate	4000	e
Two-hit time resolution	400	ns
DC leakage current tolerance	100	nA
Single channel ENC sigma (400fF)	300	e
Tuned threshold dispersion	100	e
Analog supply current/pixel @400fF	10	$\mu\text{A}$
Radiation tolerance	200	MRad
Acquisition mode	Data driven with time stamp	
Time stamp precision	8	bits
Single chip data output rate	160	Mb/s

**FE-I4 (B-layer Replacement)  
Specifications: main parameters**

# 3D silicon sensors

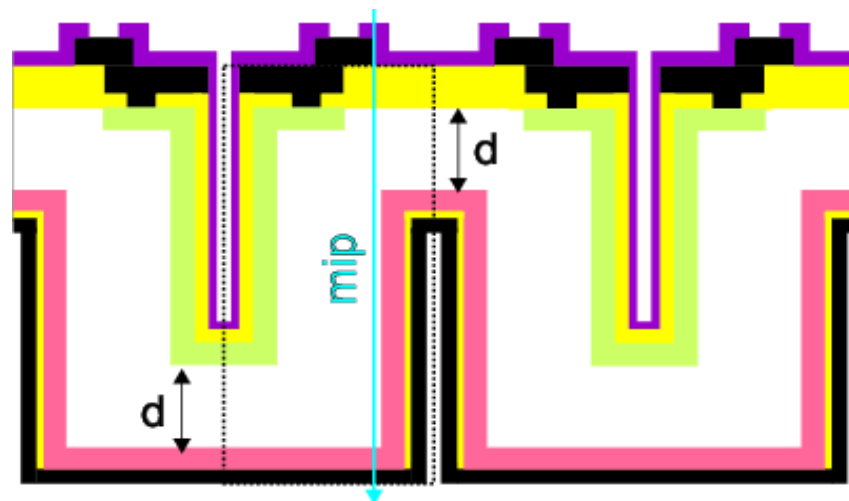
**Charge collection distance reduced**  
**→ reduced charge trapping**

Stanford/Sintef  
 ICEMOS

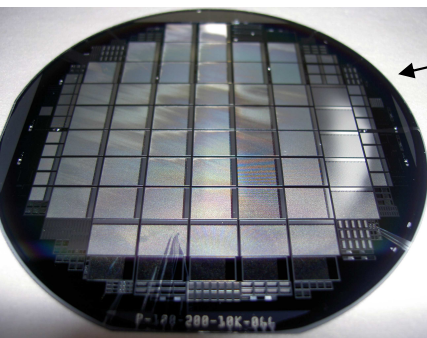


Glasgow

**Alternative geometry with double sided electrodes**

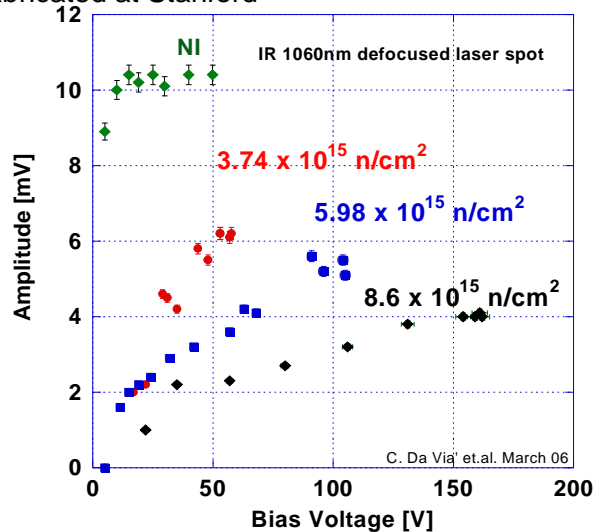


IRST  
 CNM

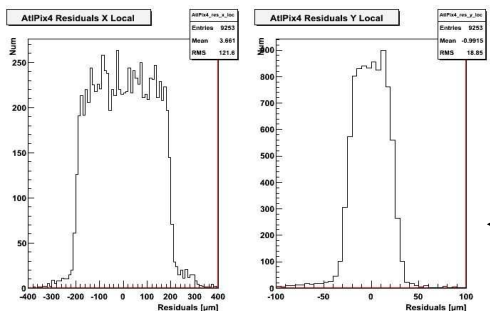
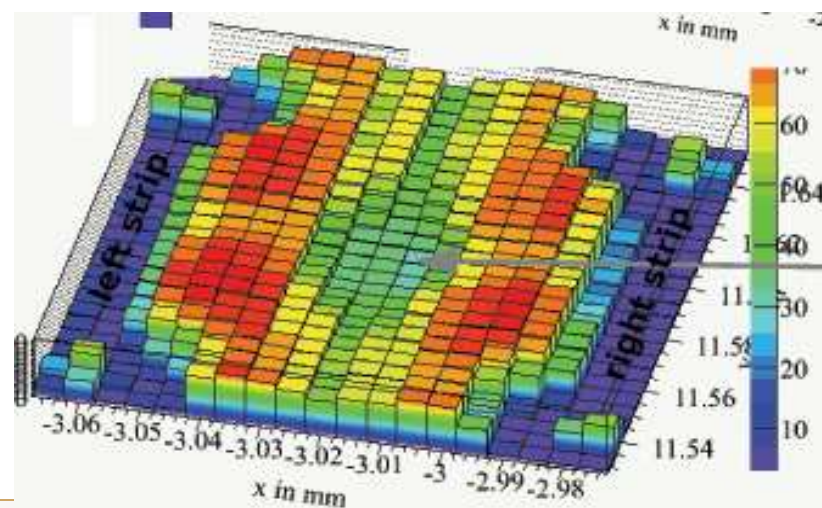


ATLAS pixel fabricated at Stanford

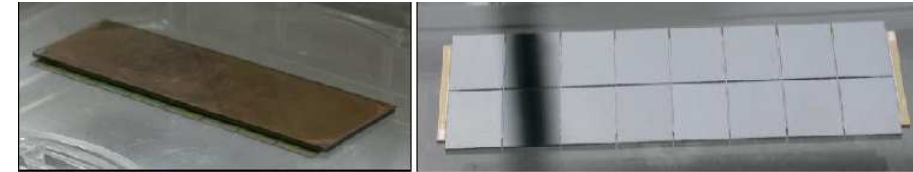
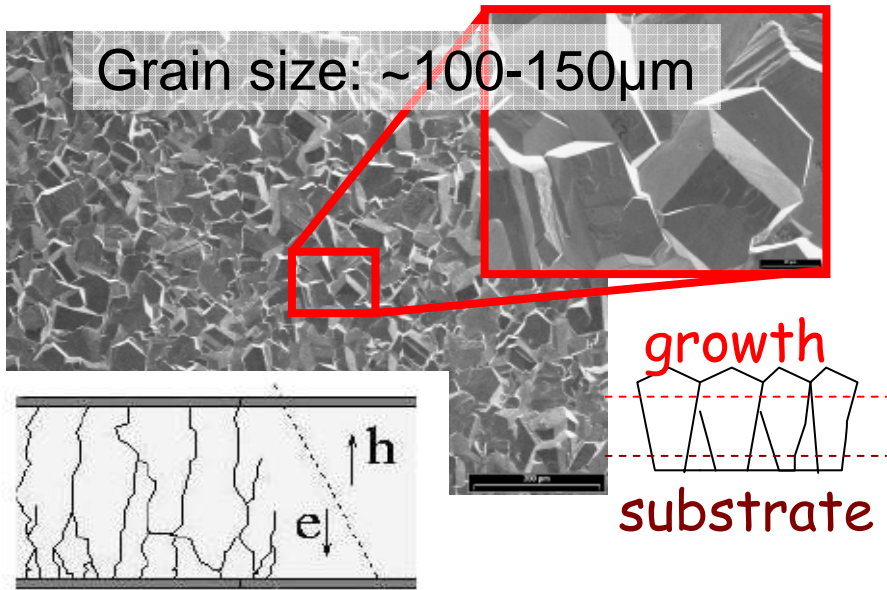
Radiation tests/Praha CCE(V) with laser



IR scan 3D- SCstrips/ Freiburg

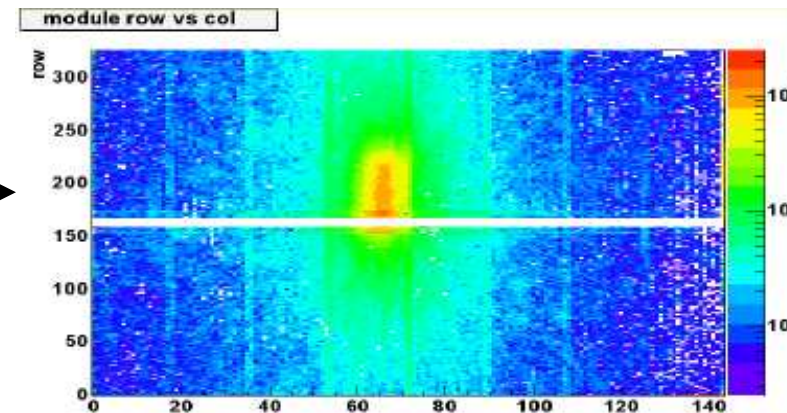


Test beam/data analysis from M. Mathes-Bonn

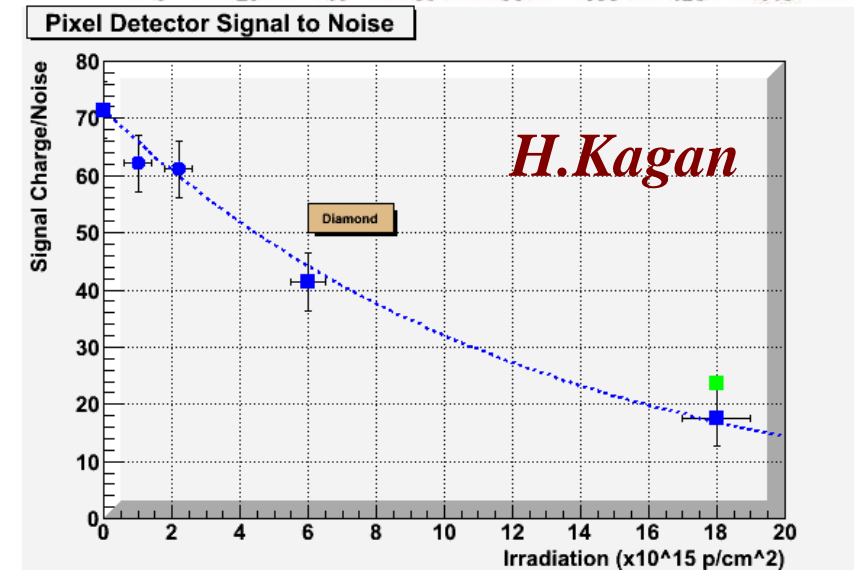


ATLAS pixel module

hitmap



- large band gap and strong atomic bonds promise fantastic radiation hardness
- low leakage current and low capacitance both give low noise
- 3 (1.5) times better mobility and 2x better saturation velocity give fast signal collection
- ionization energy is high:  $MIP \approx 2x$  less signal for same  $X_0$  of SI
  - Diamond:  $\sim 13.9ke^-$  in  $361\mu\text{m}$  (140 enc; bare threshold  $\sim 1500e^-$ )
  - SI:  $\sim 22.5 ke^-$  in  $282\mu\text{m}$
- Grain-boundaries, dislocations, and defects can influence carrier lifetime, mobility, charge collection distance and position resolution
- Available Size  $\sim 2 \times 6 \text{ cm}^2$  (12cm diameter wafer;  $\sim 2\text{mm}$  thick)





# Some Compilation Plots

Planar n-in-n or n-in-p:

3D- sensors:

Diamond:

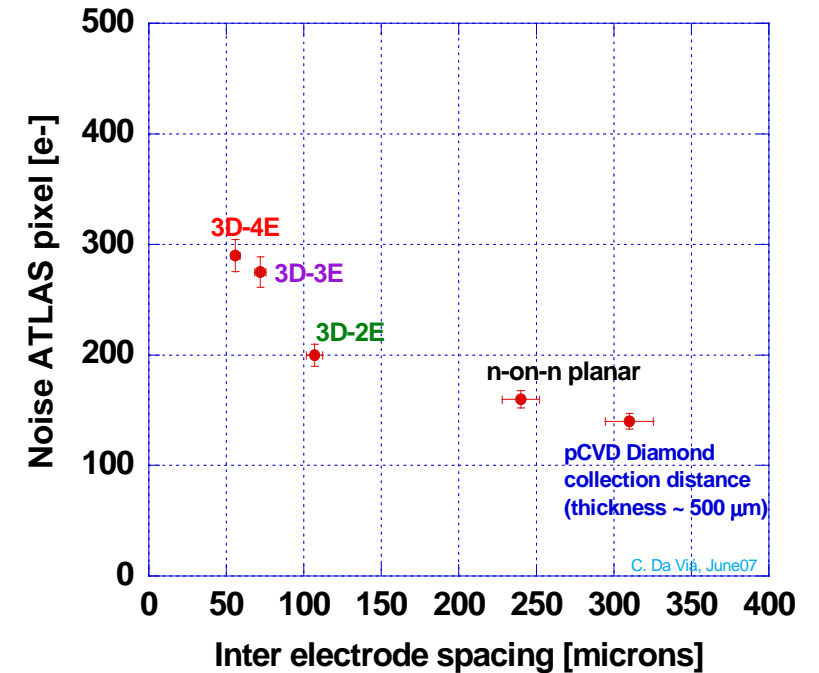
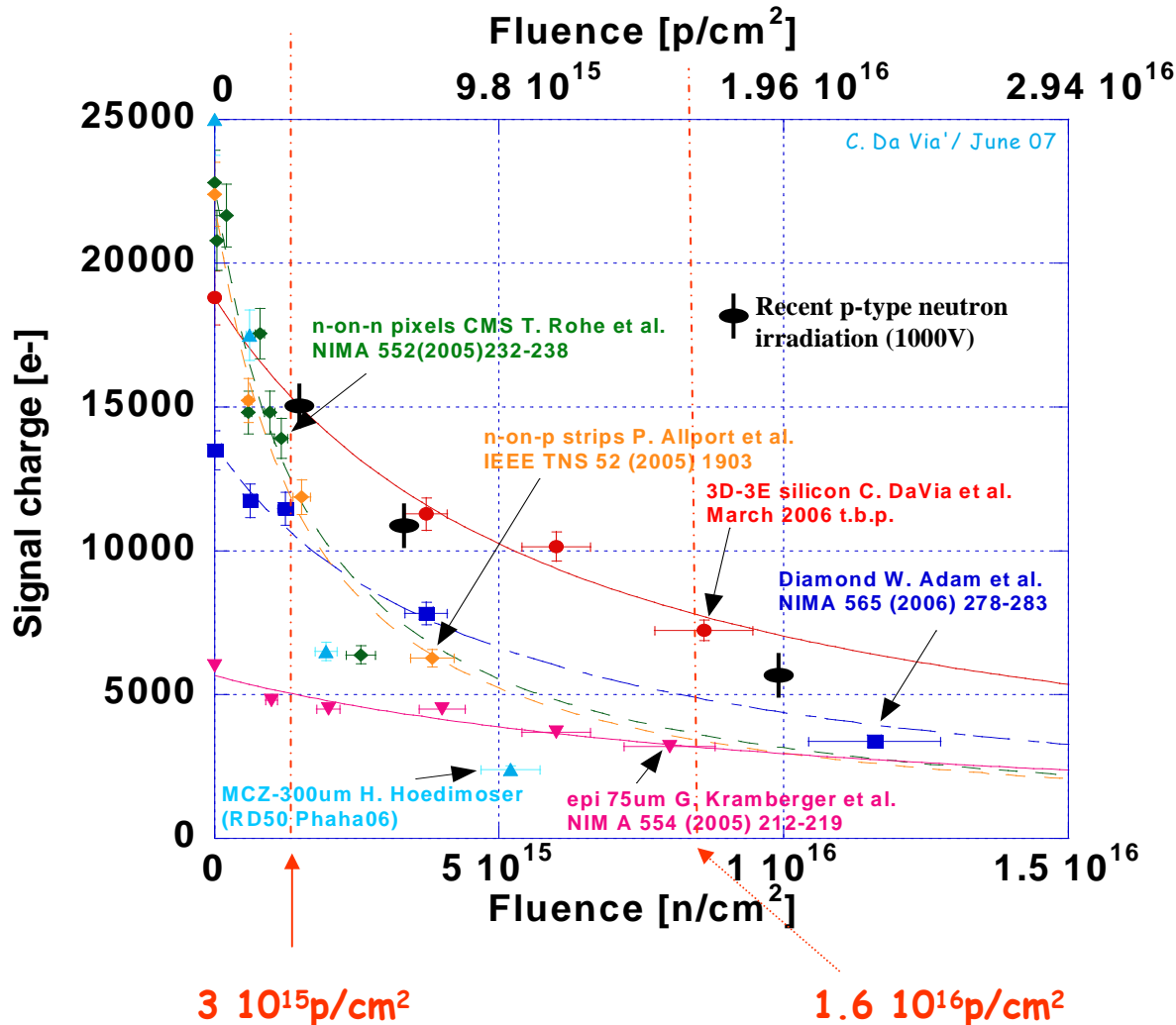
Comparisons of minimum ionising particle (m.i.p.) CCE(V) and S/N after  $10^{16}n_{eq}/cm^2$  needed

## My comments

Conservative solution but high operating voltages: can thin help?

Highest signal (Efficiency in columns? Commercial fabrication?)

Lower currents, low noise (Cost? Uniformity?)



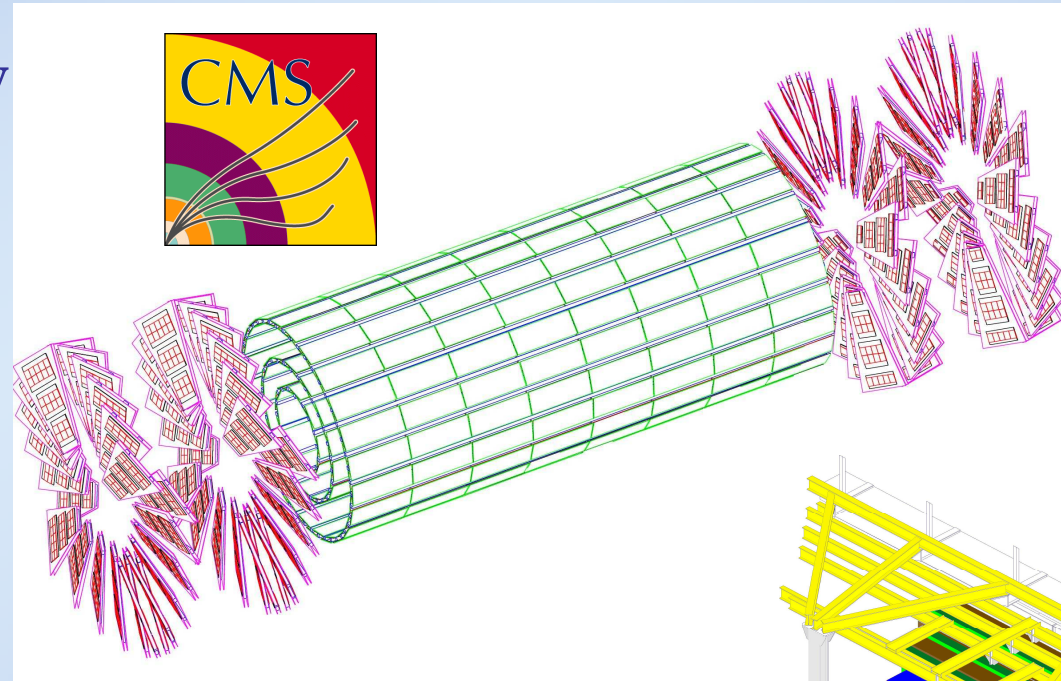
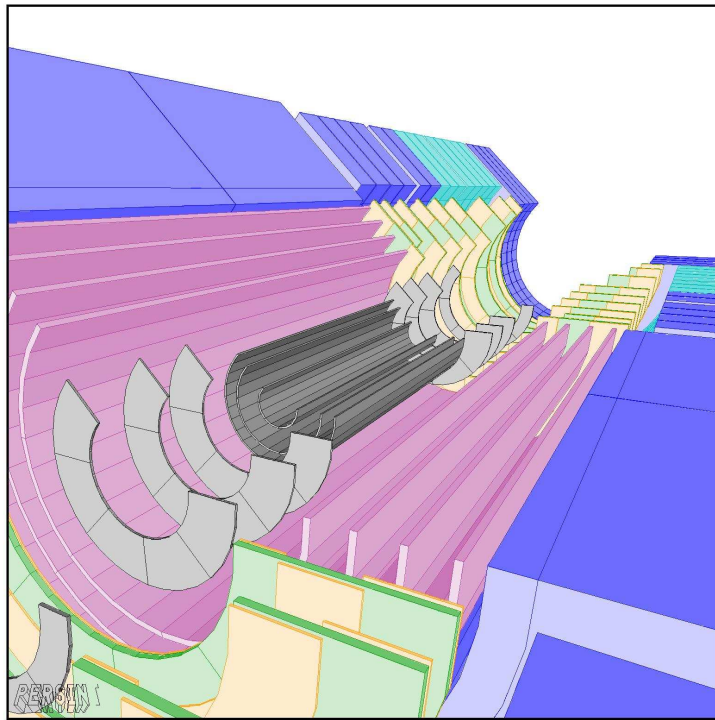
## Atlas pixel assemblies

- Noise figure is very good for diamond
- 3D can still play with the substrate thickness
- Planar n-on-p can still play a role in case above technologies not ready

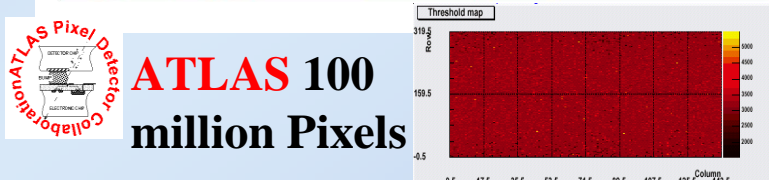
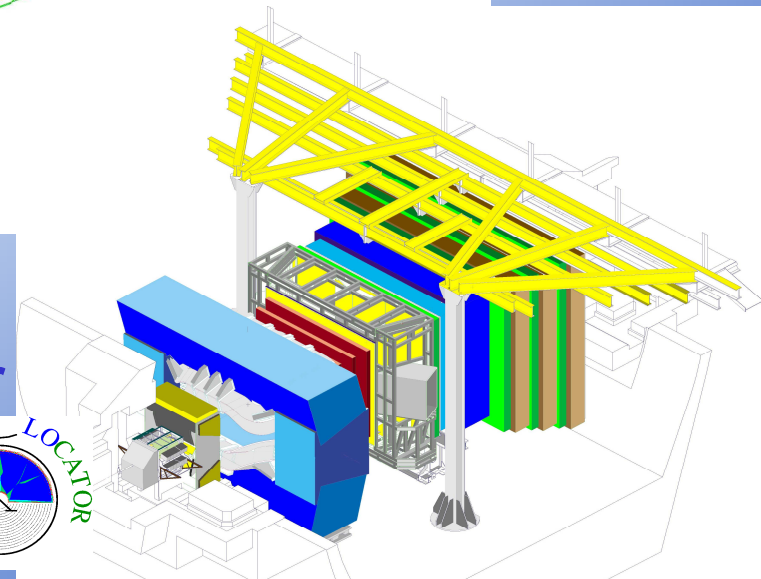
# Innermost Detectors at Current LHC

LHC vertex detectors all use  $n^+$  implants in  $n^-$  bulk:

- Because of advantages after heavy irradiation from collecting electrons on  $n^+$  implants, the detectors at the LHC (ATLAS and CMS Pixels and LHCb Vertex Locator) have all adopted the  $n^+$  in  $n^-$  configuration for doses of  $5 - 10 \times 10^{14} n_{eq} cm^{-2}$
- Requires 2-sided lithography



LHCb  
Vertex Locator  
Z(mm)=0-990



# Motivations for P-type

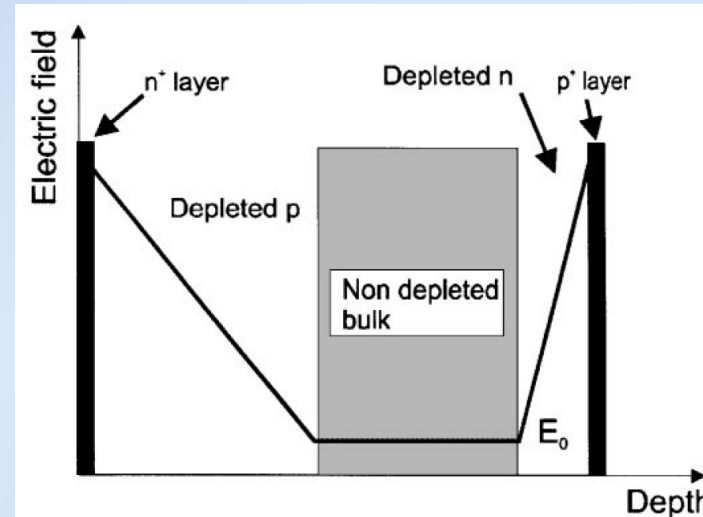
**Starting with a p<sup>-</sup>-type substrate offers the advantages of single-sided processing while keeping n<sup>+</sup>-side read-out:**

- **Processing Costs (~50% cheaper).**
- **Greater potential choice of suppliers.**
- **High fields always on the same side.**
- **Easy of handling during testing.**
- **No delicate back-side implanted structures to be considered in module design or mechanical assembly.**

**So far, capacitively coupled, polysilicon biased devices fabricated to ATLAS mask designs with Micron Semiconductor (UK) Ltd (full size: 6cm×6cm), CNM Barcelona (miniature: 1cm×1cm), ITC Trento (miniature: 1cm×1cm) and Hamamatsu Photonics (1cm×1cm and orders placed for 10cm×10cm ATLAS prototypes)**

# N-side read-out for tracking in high radiation environments?

Schematic changes of Electric field after irradiation



Effect of trapping on the Charge Collection Efficiency (CCE)

$$Q_{tc} \cong Q_0 \exp(-t_c/\tau_{tr}), \quad 1/\tau_{tr} = \beta\Phi.$$

Collecting electrons provide a sensitive advantage with respect to holes due to a much shorter  $t_c$ . P-type detectors are the most natural solution for  $e$  collection on the segmented side.

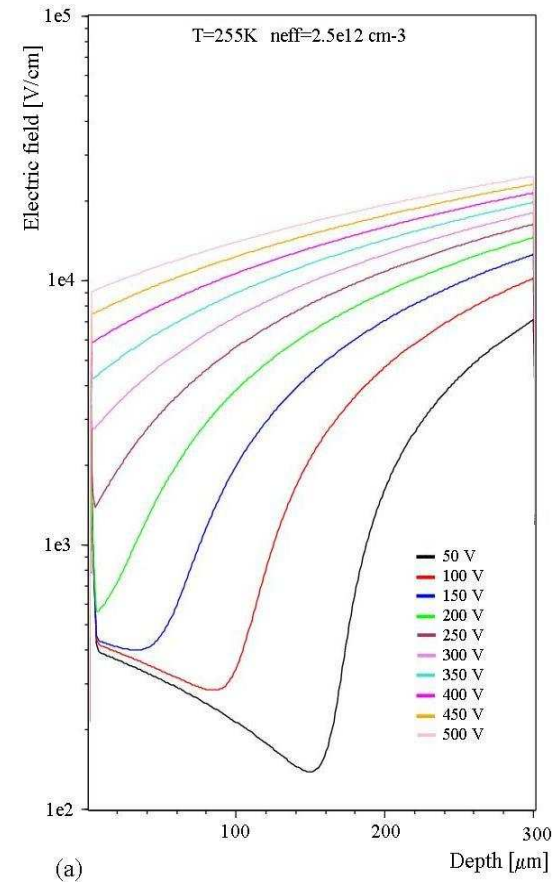
N-side read out to keep lower  $t_c$

# More realistic simulation (ISE-TCAD) of E of an irradiated detector.

P-type devices have always the high field region on the **right side**.

P-side

N-side



Effect of trapping on  
the Charge Collection  
Distance

$$Q_{tc} \cong Q_0 \exp(-t_c/\tau_{tr}), \quad 1/\tau_{tr} = \beta\Phi.$$

$$V_{sat,e} \times \tau_{tr} = \lambda_{av}$$

$$\beta_e = 4.2E-16 \text{ cm}^{-2}/\text{ns}$$

$$\beta_h = 6.1E-16 \text{ cm}^{-2}/\text{ns}$$

From G. Kramberger et al., NIMA  
476(2002), 645-651.

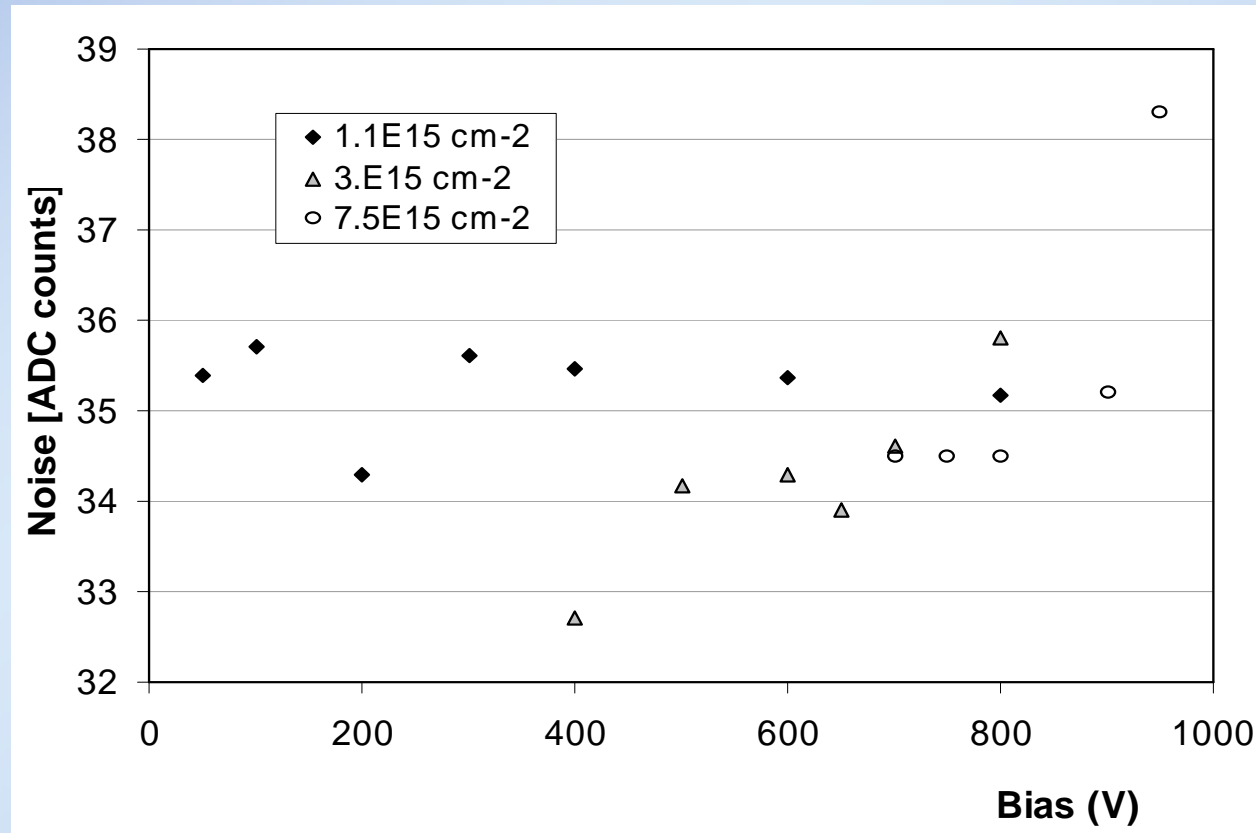
After heavy  
irradiation thin  
detectors should  
have a similar CCE  
as thicker ones.

$$\lambda_{av} (\Phi=1e14) \cong 2400\mu\text{m}$$

$$\lambda_{av} (\Phi=1e16) \cong 24\mu\text{m}$$

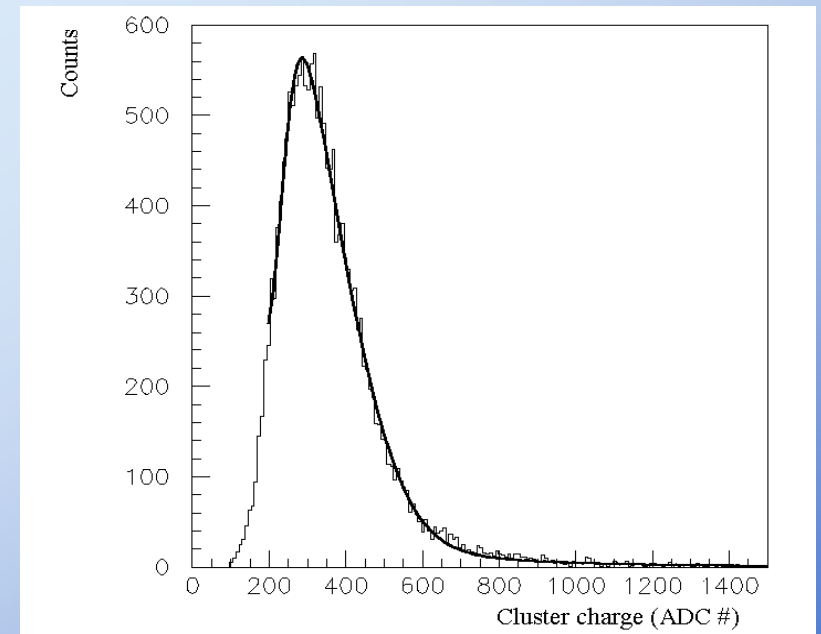
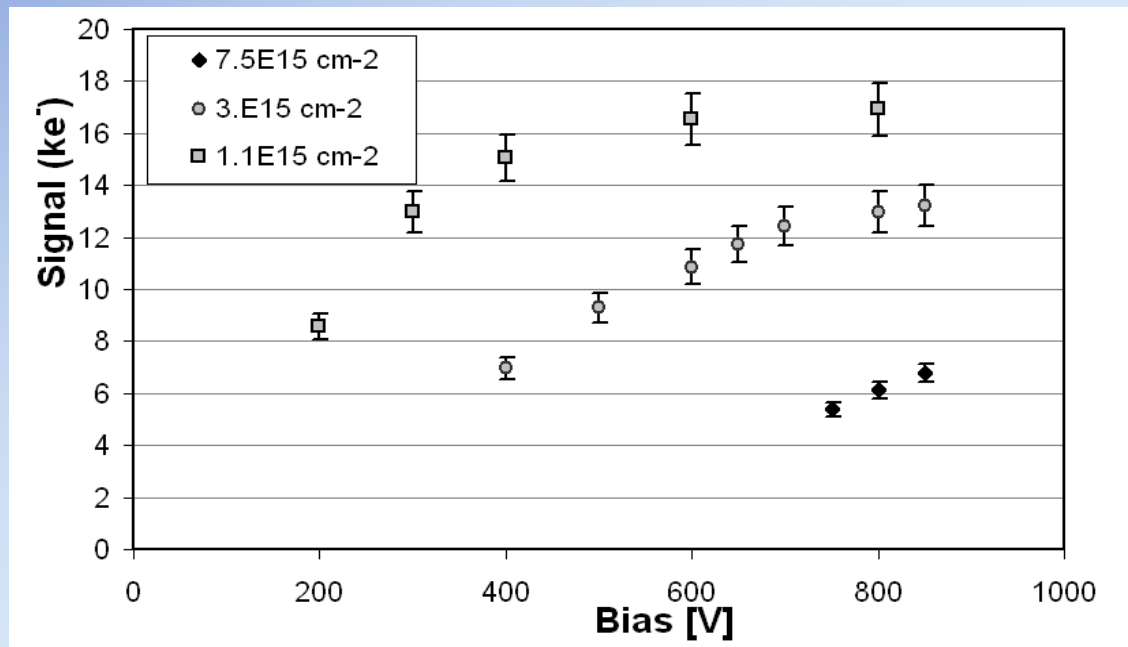
# P-type miniature detectors from CNM

Despite the rather poor pre-irradiation characteristics, all the devices ( $\sim 300\mu\text{m}$  thick) show a remarkable robustness, after irradiation, both in term of breakdown voltage and noise. A value of about 34 ADC counts was the typical one measured with similar geometry standard ATLAS non-irradiated miniature sensors.



# P-type miniature detectors from CNM

Extremely good performances in term of charge collection after unprecedented doses (1., 3.5., and 7.5  $10^{15}$  p  $\text{cm}^{-2}$ ) are shown.



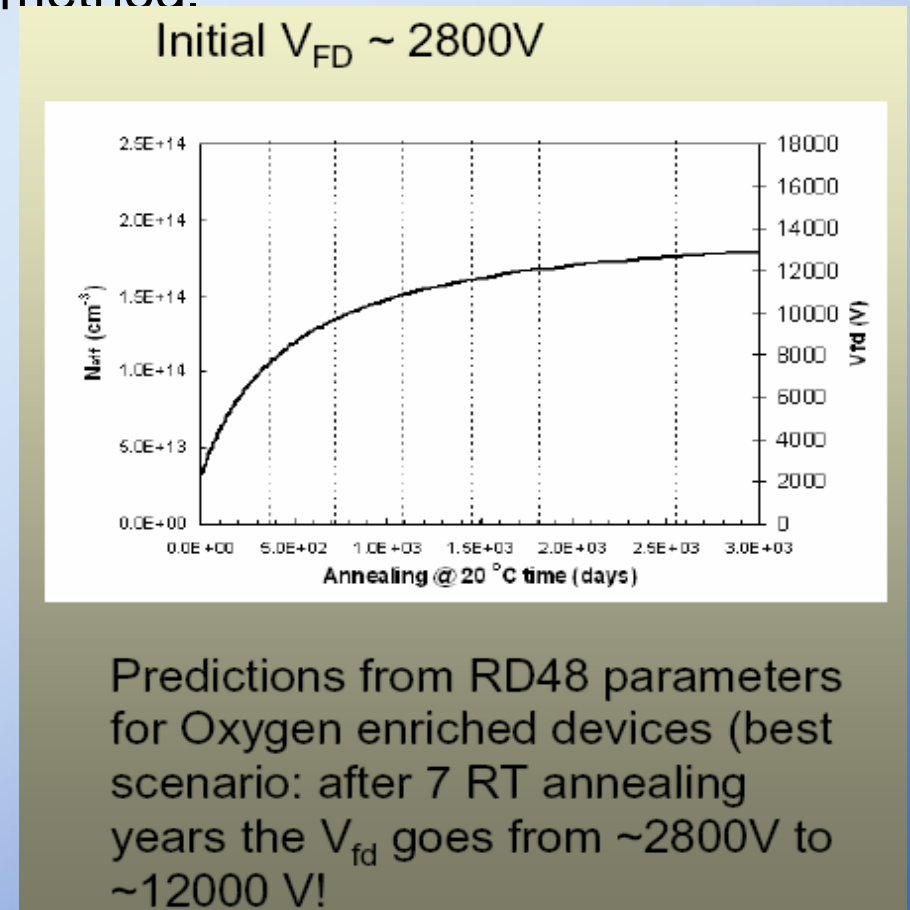


# P-type miniature detectors from CNM

Another effect that has changed the way to regard at the reverse annealing has been measured on these devices. The reverse annealing has been always considered as a possible cause of early failure of Si detectors in the experiments if not controlled by mean of low temperature (not only during operations but also during maintenance/shut down periods). This was originated by accurate measurements of the annealing behaviour of the full depletion voltage in diodes measured with the CV method.

Expected changes of full depletion voltage with time after irradiation (as measured with the C-V method) for detector irradiated to  $7.5 \cdot 10^{15} \text{ p cm}^{-2}$ .

Please notice that according to CV measurements the so called  $V_{\text{FD}}$  changes from  $<3\text{kV}$  to  $>12\text{kV}$ !

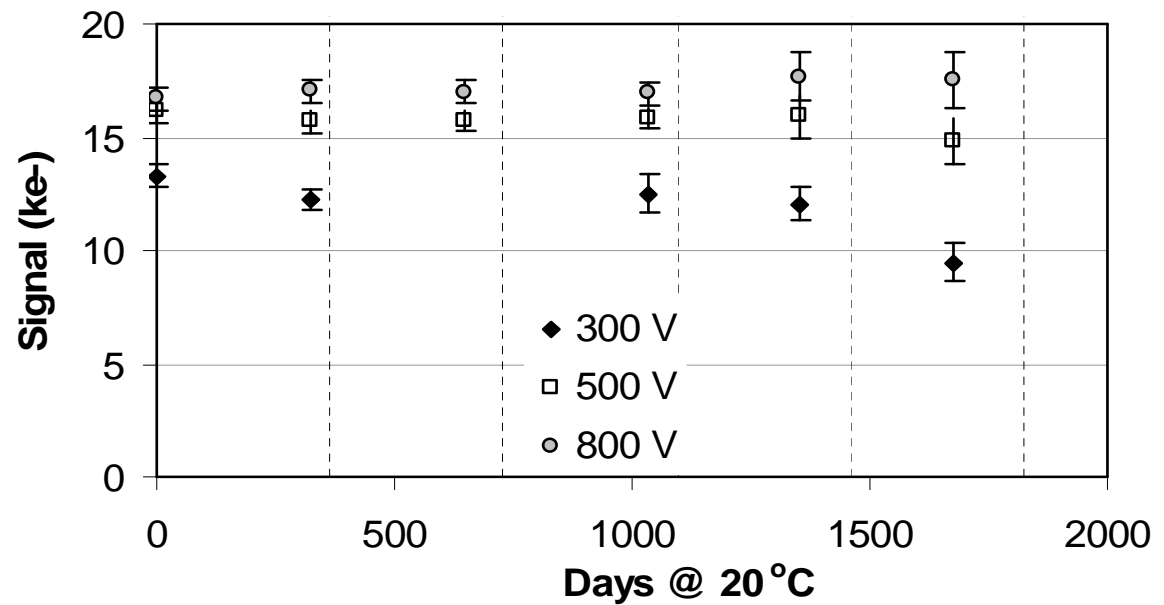
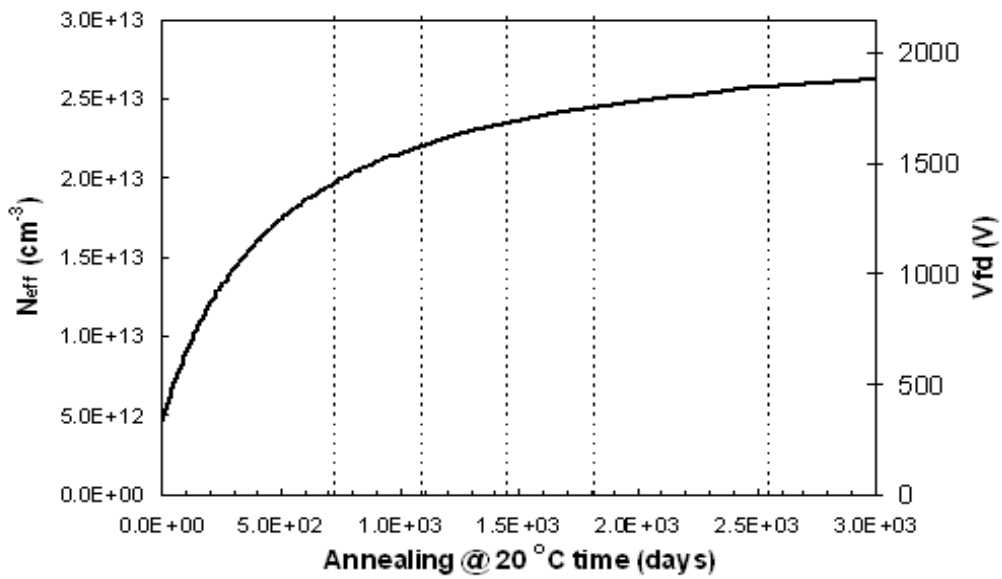
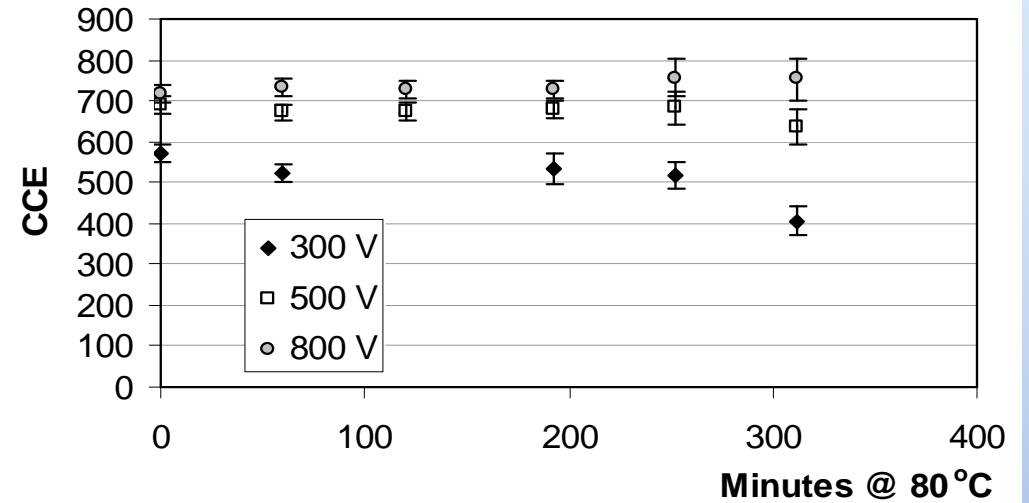


# P-type miniature detectors from CNM

**CCE annealing**  
**( $1.1 \cdot 10^{15} \text{ p cm}^{-2}$ )**

Initial  $V_{FD} \sim 420\text{V}$

Final  $V_{FD} \sim 1900\text{V}$

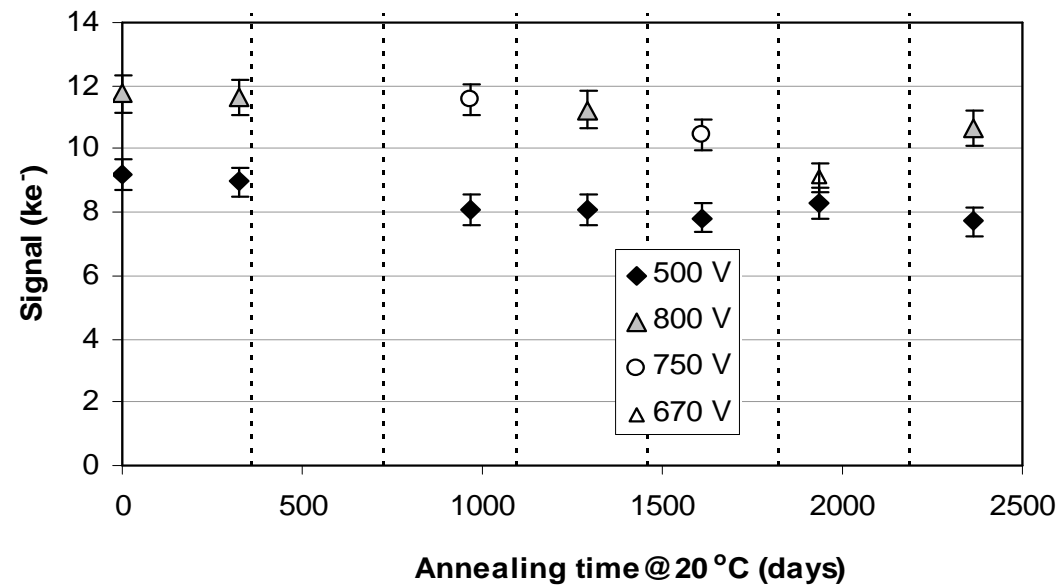
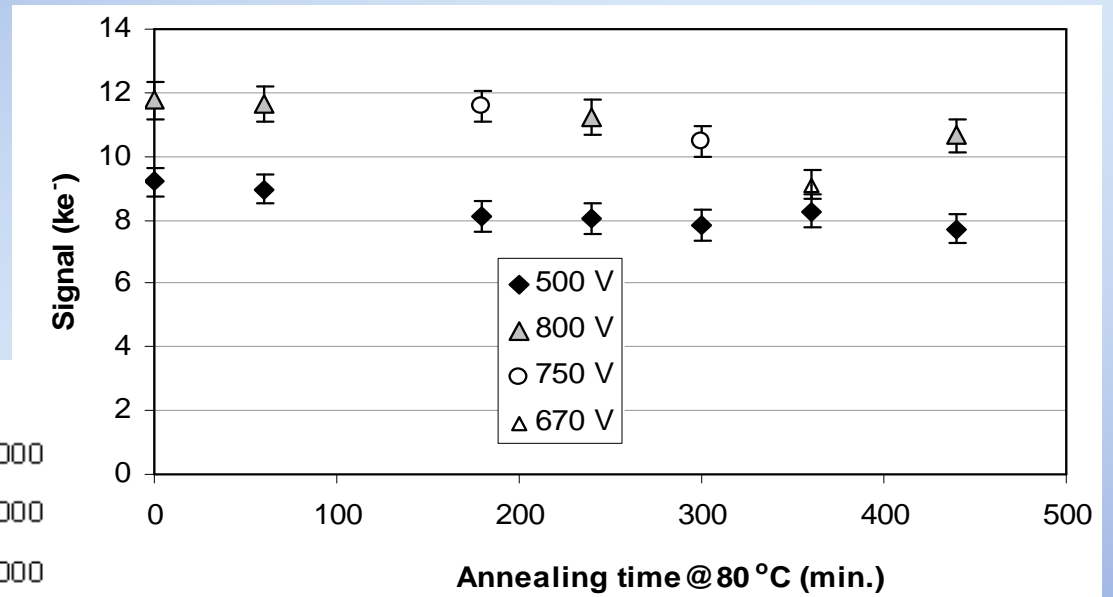
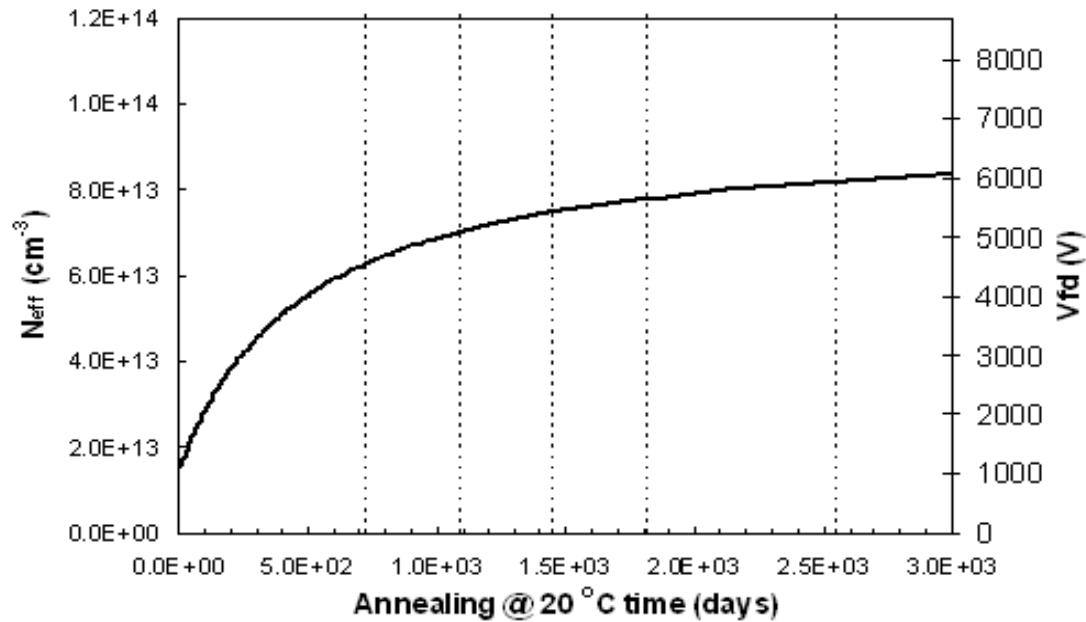


# P-type miniature detectors from CNM

$3.5 \times 10^{15} \text{ p cm}^{-2}$

Initial  $V_{FD} \sim 1300\text{V}$

Final  $V_{FD} \sim 6000\text{V}$

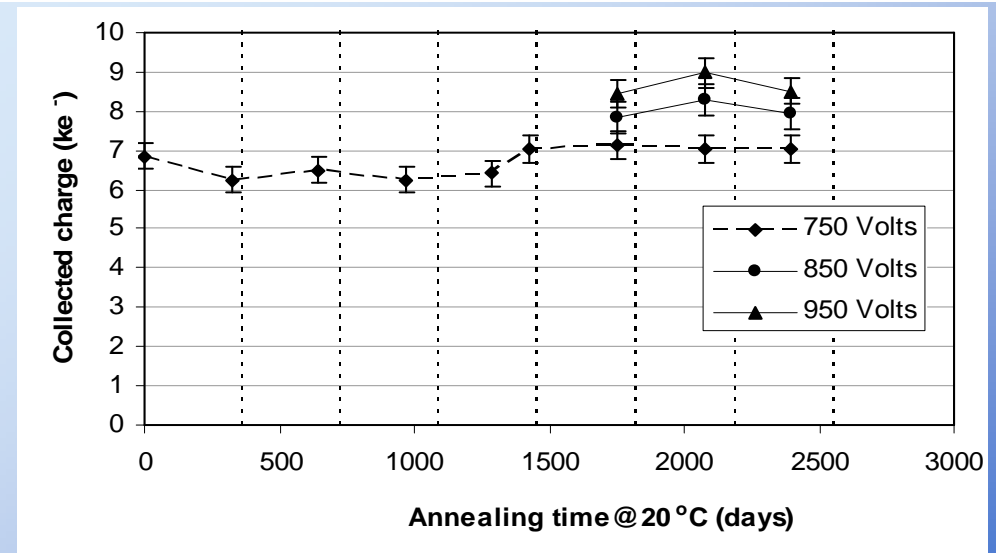
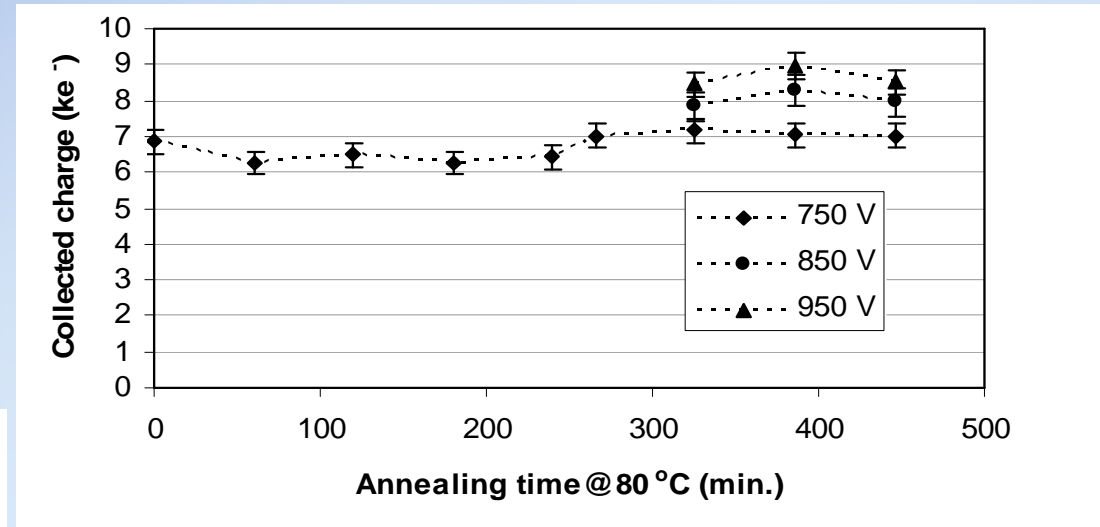
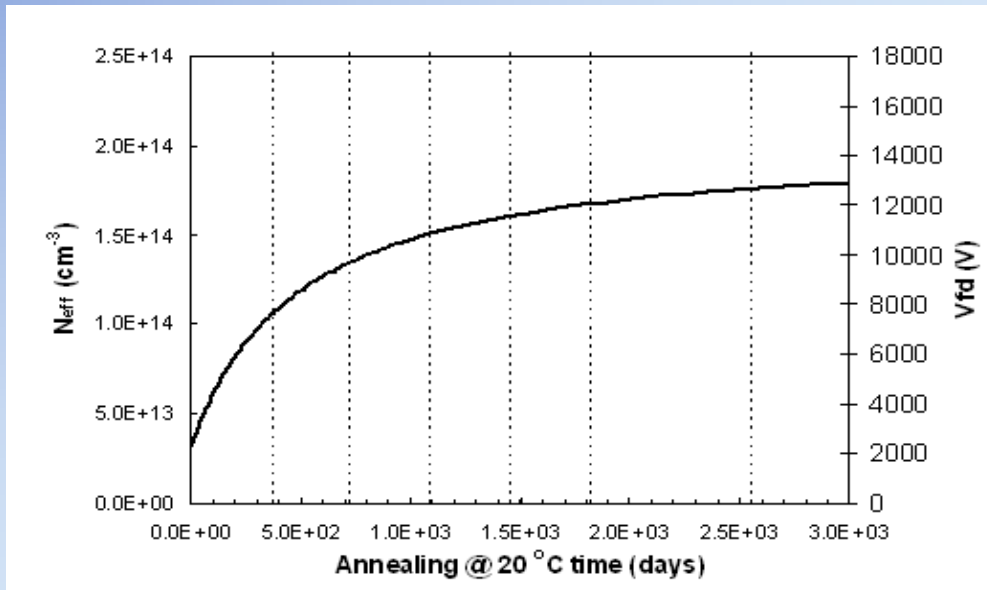


# P-type miniature detectors from CNM

$7.5 \cdot 10^{15} \text{ p cm}^{-2}$

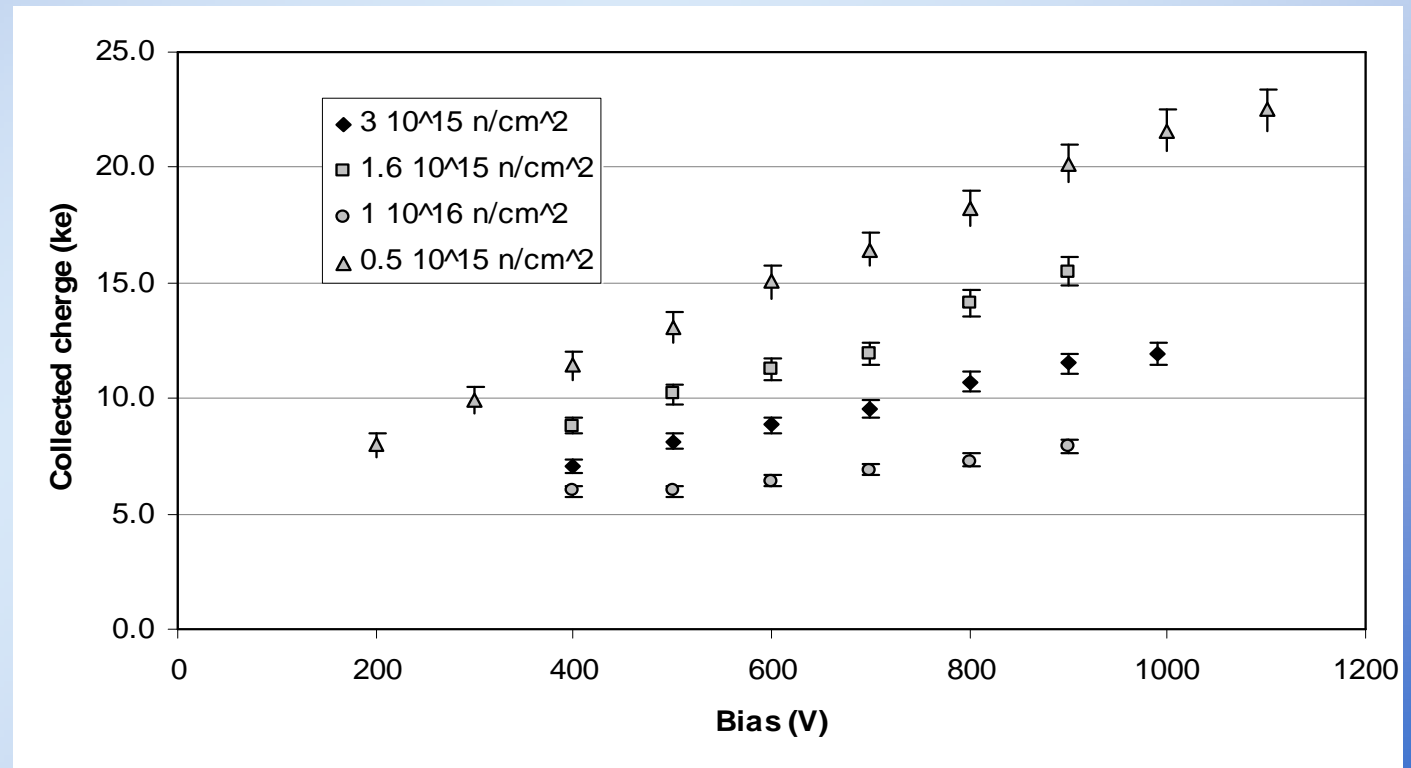
Initial  $V_{FD} \sim 2800\text{V}$

Final  $\sim 12000 \text{ V!}$

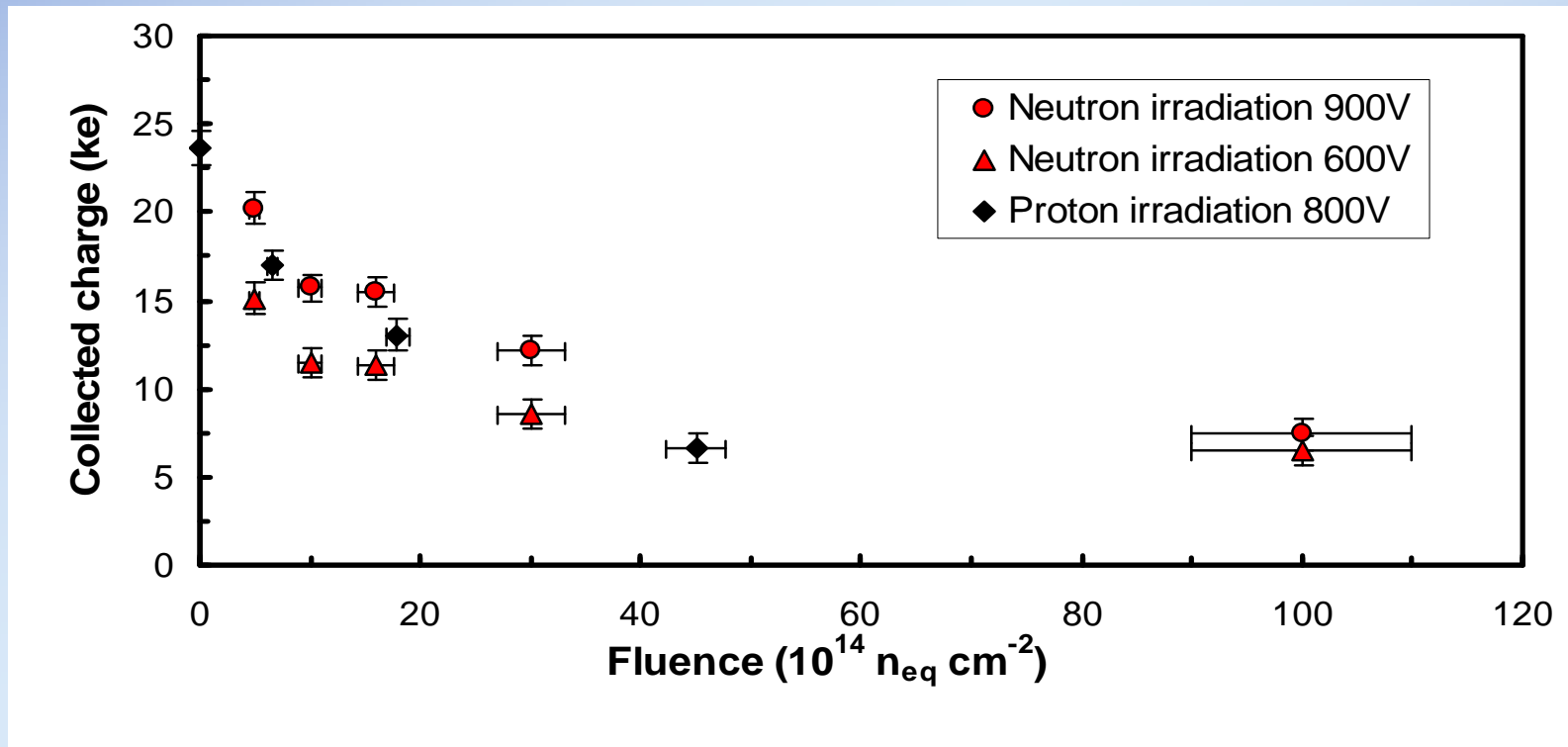


# Results with neutron irradiated Micron detectors

Now  $\mu$ -strip detector  
CCE measurements  
up to  $1 \times 10^{16}$  n  $\text{cm}^{-2}$ !!



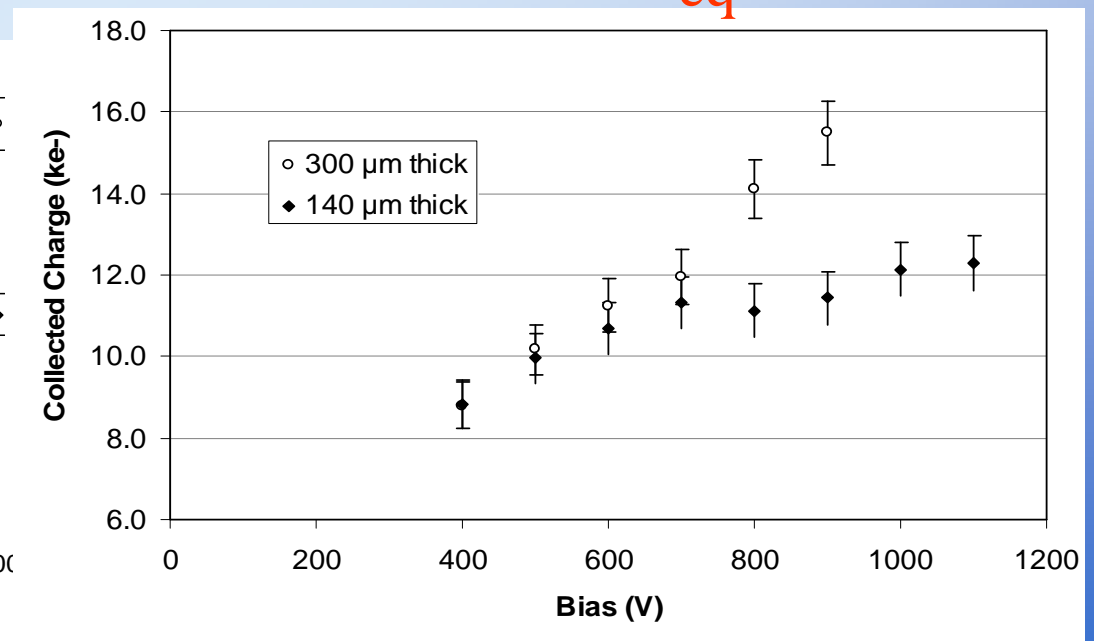
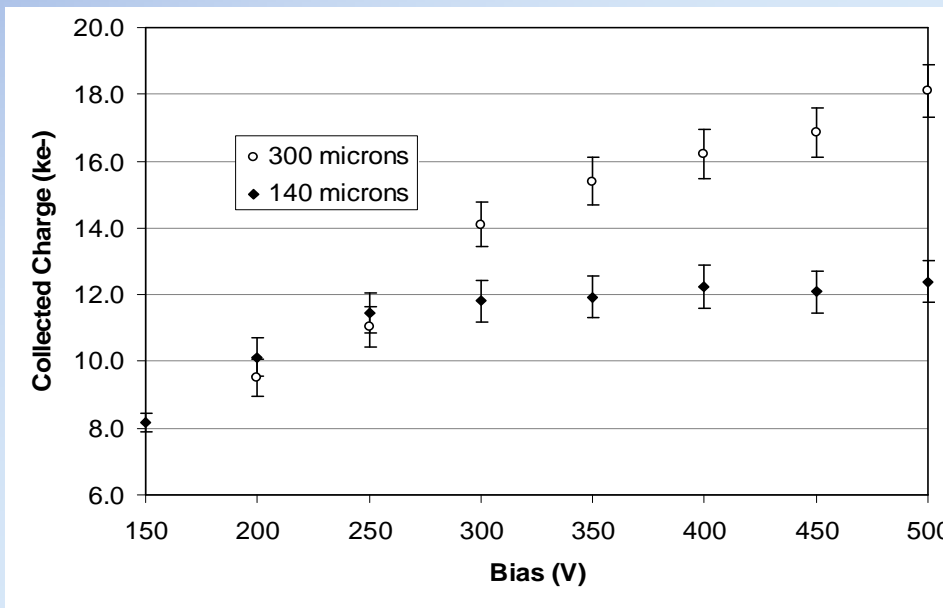
# Charge collection efficiency vs fluence for micro-strip detectors irradiated with n and p read-out at LHC speed (40MHz, SCT128 chip).



# Comparison of CCE with 140 $\mu\text{m}$ and 300 $\mu\text{m}$ thick detectors from Micron irradiated to various n fluences, up to $1 \times 10^{16} \text{ cm}^{-2}$

$5 \times 10^{14} (?) n_{\text{eq}} \text{ cm}^{-2}$

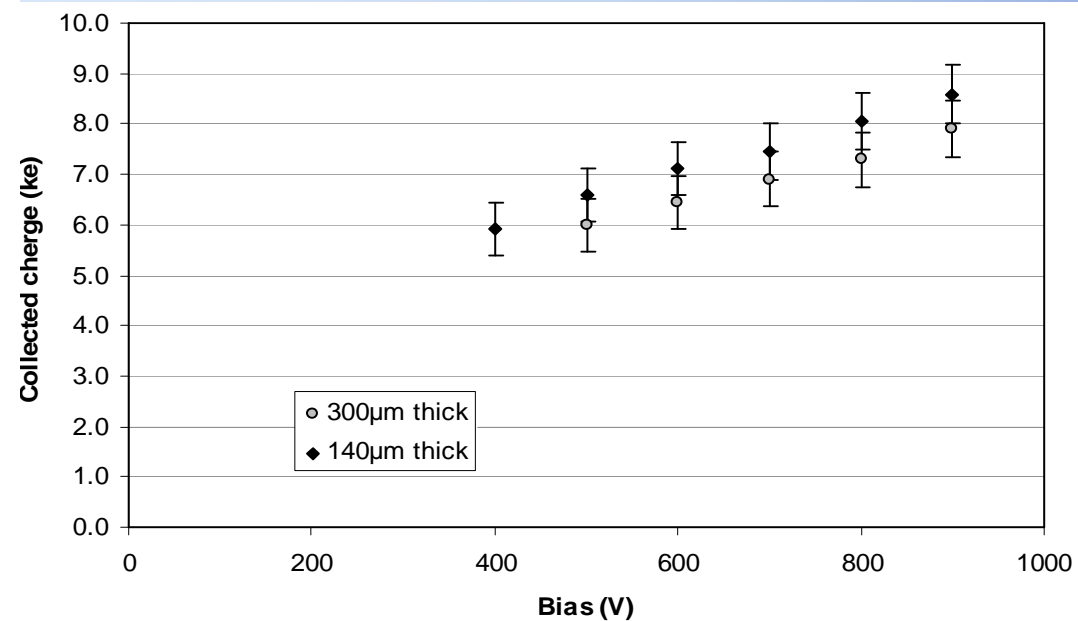
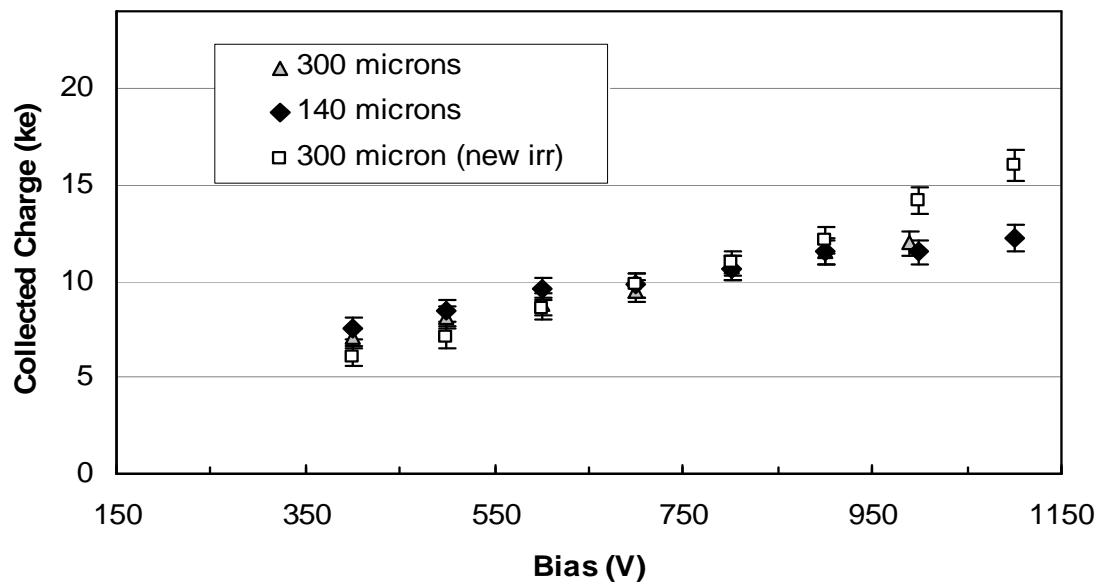
$1.6 \times 10^{15} n_{\text{eq}} \text{ cm}^{-2}$



# Comparison of CCE with 140 $\mu\text{m}$ and 300 $\mu\text{m}$ thick detectors from Micron irradiated to various n fluences, up to $1 \times 10^{16} \text{ cm}^{-2}$

$3 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$

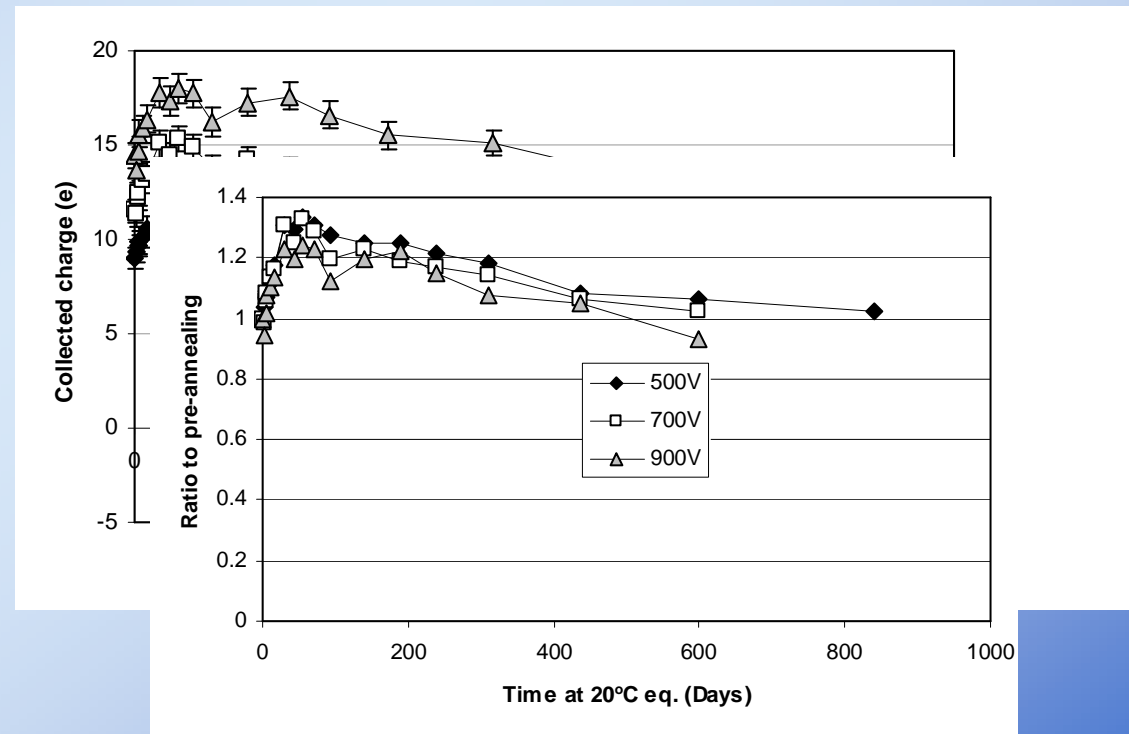
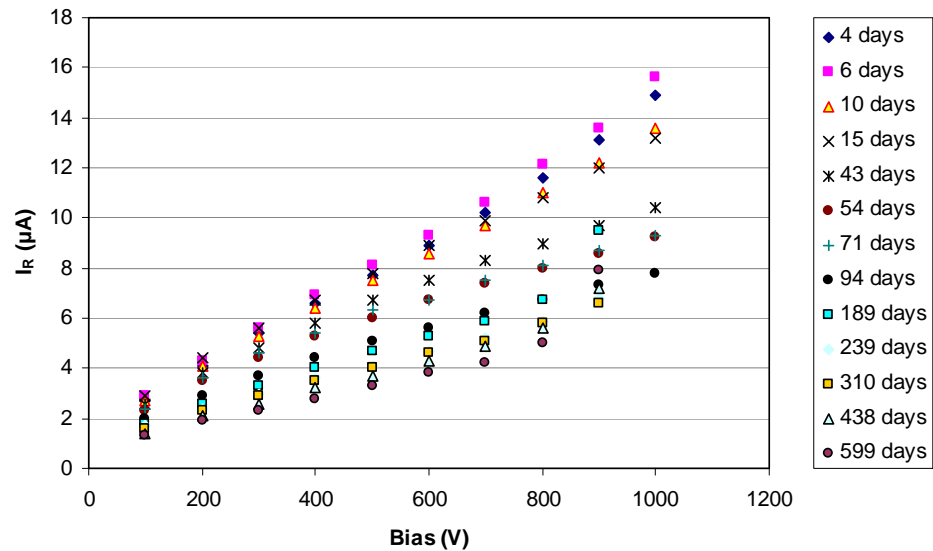
$1 \times 10^{16} \text{ n}_{\text{eq}} \text{ cm}^{-2}$





# Operational parameters: temperature history

Essential to keep at  $-20/25^{\circ}\text{C}$  during operation for reducing the runaway probability and shot noise increase. But in shut down period? The previous slides on annealing were taken with rough granularity. A detailed study of the annealing has been performed, and the results are quite impressive, in term of recovery of charge collection with neutron irradiated detectors.



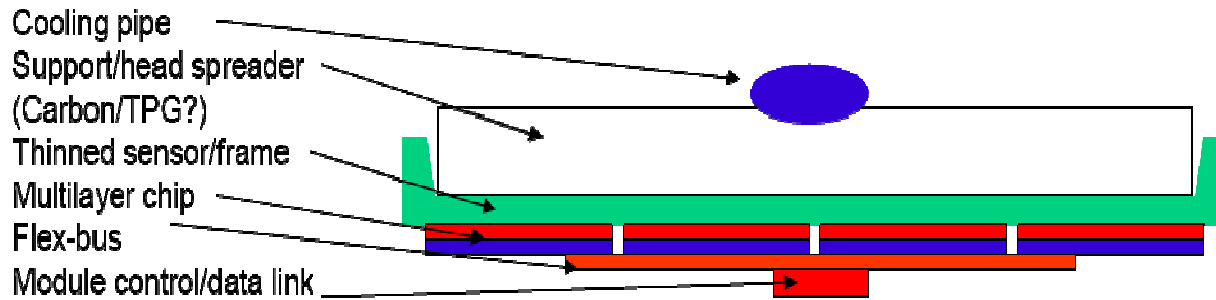
# Microstrip Front-end ASIC (ABCn)

## Design Status

Front-End	Opt. short strip done Layout started	33mA/chip ✓ 750enc (2.5cm strips) Final S/N > 10 ✓
Back-End	Main change in DCL block to handle 160MHz	92mA/chip at 2.5V estimated
Powering	Integrated shunt regulators possible	Current limits to impose uniformity
Floor Plan	First Checks now	7.5mm by 6±1mm
P&R	Examples with pipeline and derandomizer OK	
Submission	Scheduled January 2008	Deliver by April

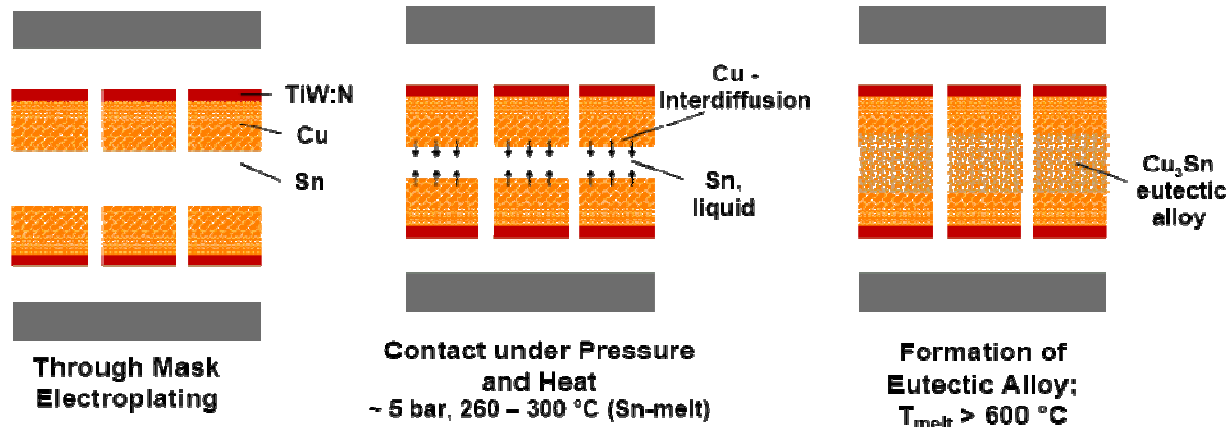
# Thin Sensors and Vertical Integration

A sketch of the module concept

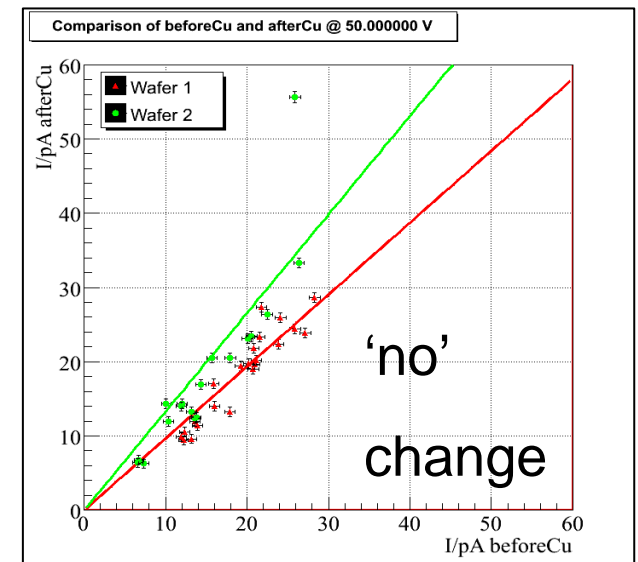
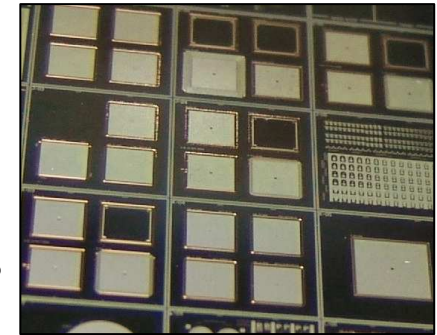


- 1) Low  $I_{leak}$ , low  $V_{dep}$
- 2) Large live-fraction
- 3) SLID interconnection
- 4) 3D integration

## Solid Liquid Interdiffusion (SLID), IZM Munich



First diodes



*R. Nisius*

Conducted by: Bonn, Dortmund, MPI, Oslo, Interon, IZM

# Detectors for sLHC

**G. Casse**

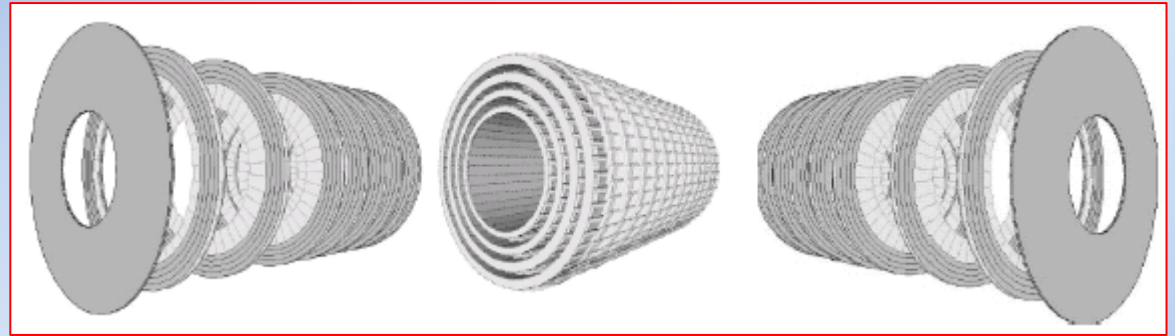
**University of Liverpool Group**

**6<sup>th</sup> December 2007**

- **Proposed Tracker Layout and Simulations  
(Radiation and Occupancy)**
- **Sensor and FE Electronics R&D**
- **Microstrip Module and Engineering Concepts**
- **Power, DCS, Opto-electronics, Services, Cooling, ...**
- **Conclusions**

# Current SCT ATLAS Module Designs

**ATLAS Tracker Based on Barrel and Disc Supports**



**Effectively two styles of modules (with 2×6cm long strips)**

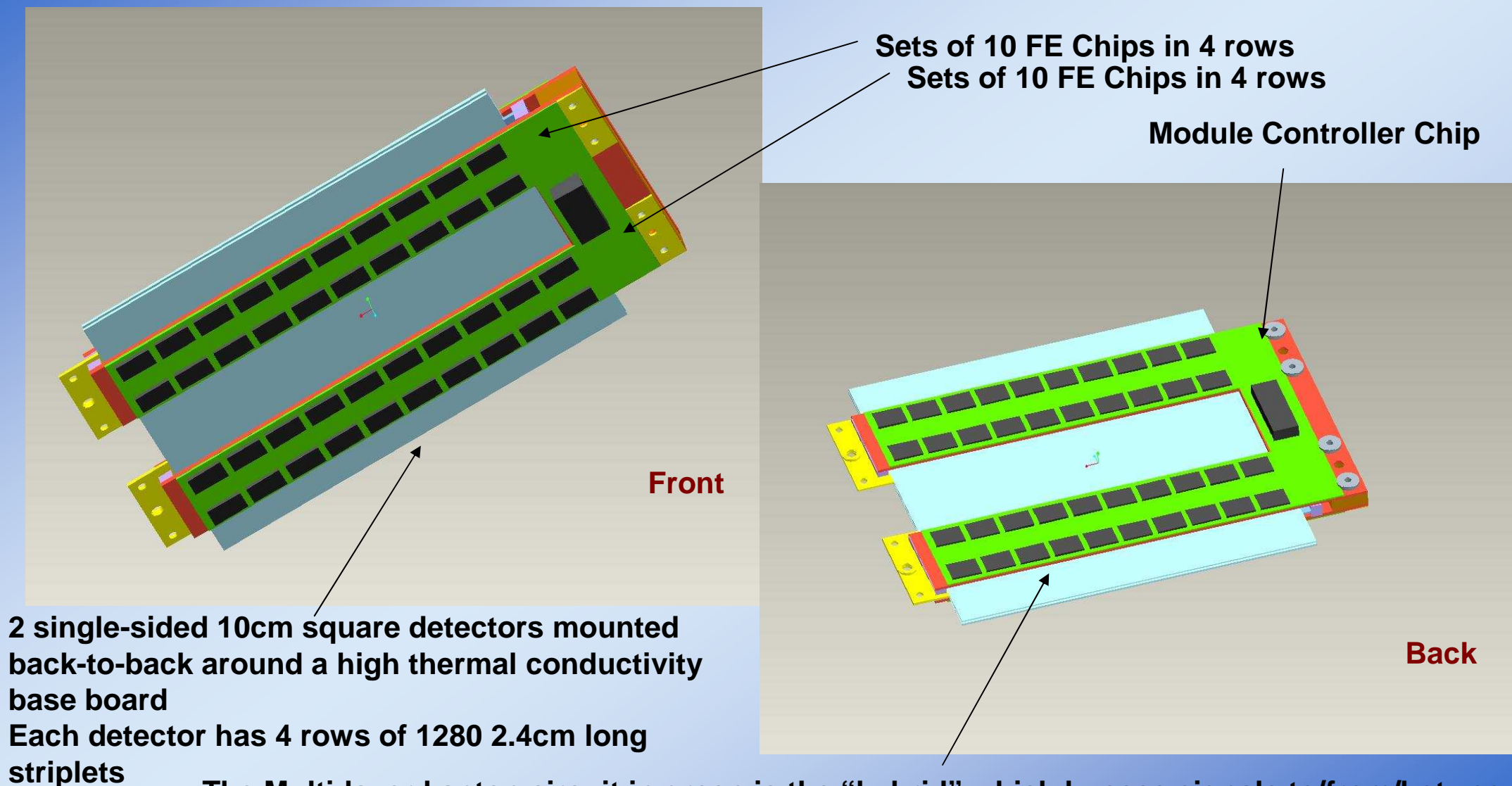


**Barrel Modules**  
(Hybrid bridge above sensors)



**Forward Modules**  
(Hybrid at module end)

# Super-LHC Double Sided Module



The Multi-layer kapton circuit in green is the "hybrid" which busses signals to/from/between the microchips and provide the electrical services to the front end electronics  
Wire bonds connect the electronics to the hybrid and provide the high density connections down from the front-end to the 4 pad rows on the detectors

# New HPK Sensor ATLAS07 Order

- Strip segments

- 4 rows of 2.38 cm strips (each row 1280 channels)

- Dimension

- Full square

- Wafer

- 150 mm p-type FZ(100)
- 138 mm dia. usable
- 320  $\mu$ m thick

- Axial strips

- 74.5  $\mu$ m pitch

- Stereo strips

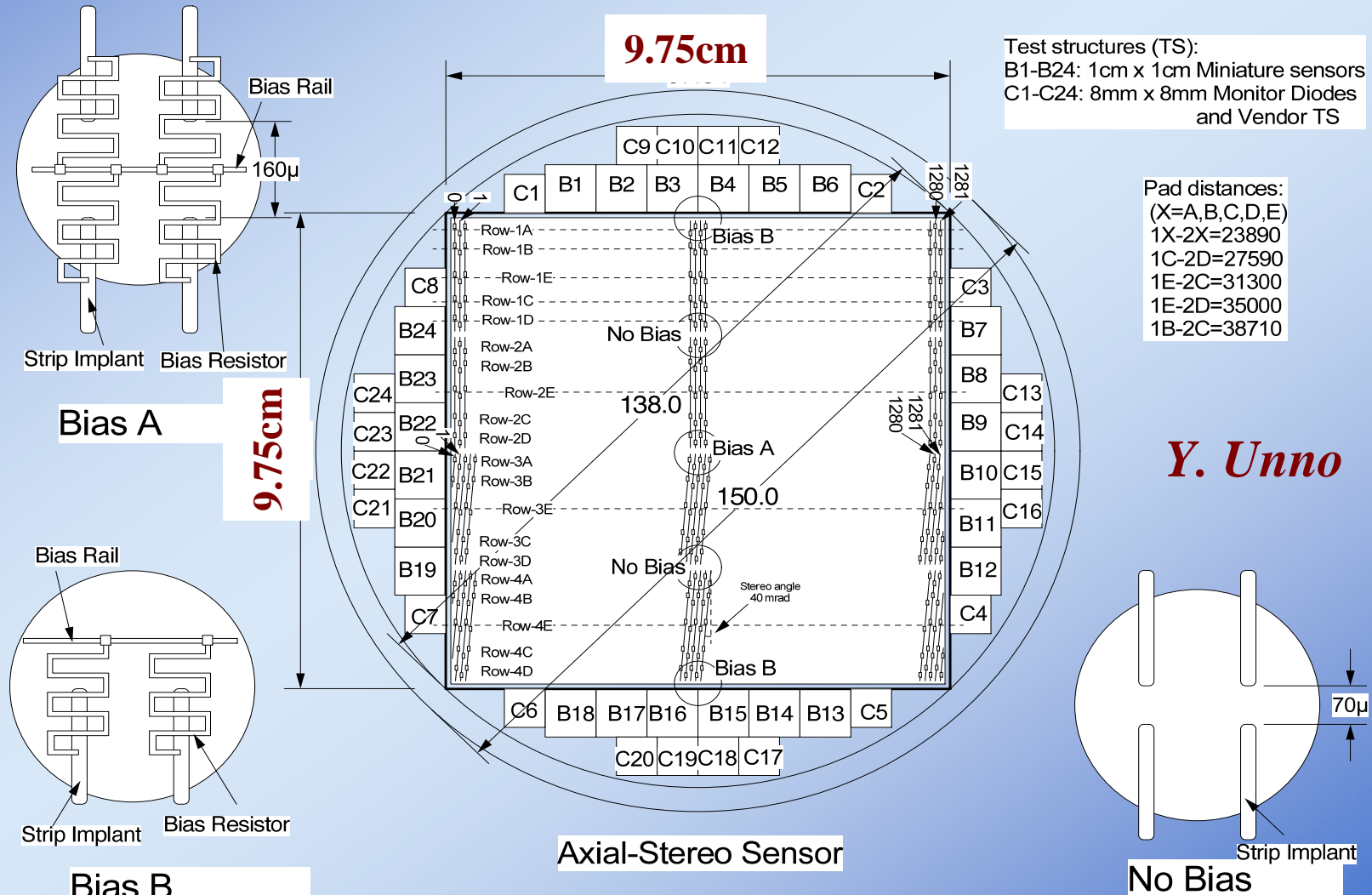
- 40 mrad
- 71.5  $\mu$ m pitch

- Bond pads location

- accommodating 24-40 mm distances

- n-strip isolation

- P-stop
- Spray on miniatures



Sensors	Presenes		Split1		Split2		Split3		Total
	p-stop	p-spray+p-stop	p-stop		p-spray+p-stop		p-spray+p-stop removed		
Wafer	FZ1		FZ1	FZ2	FZ1	FZ2	FZ1	FZ2	
Main sensors	6	6	35	40	8	13	14	13	135
Miniature sensors (Zone 1,2,3 inclusive)	72	72	420	480	96	156	168	156	1620
Test structures	12	12	20	20	20	20	20	20	144
Monitored diodes	12	12	20	20	20	20	20	20	144
Total	102	102	485	560	144	209	222	209	2043

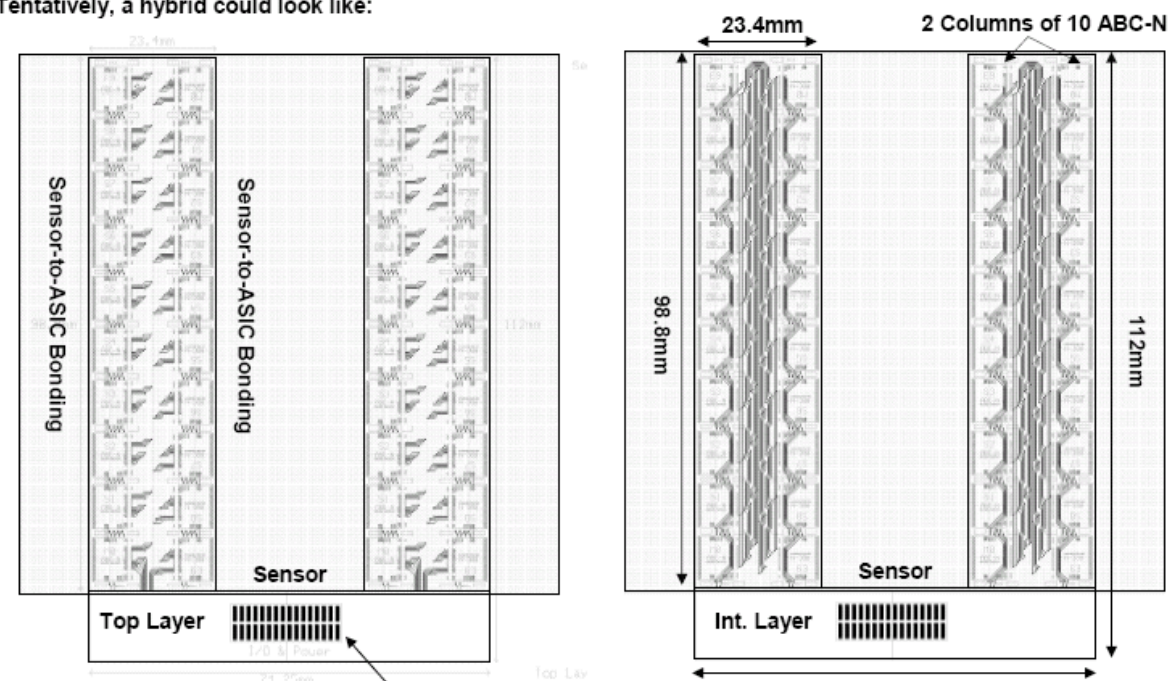
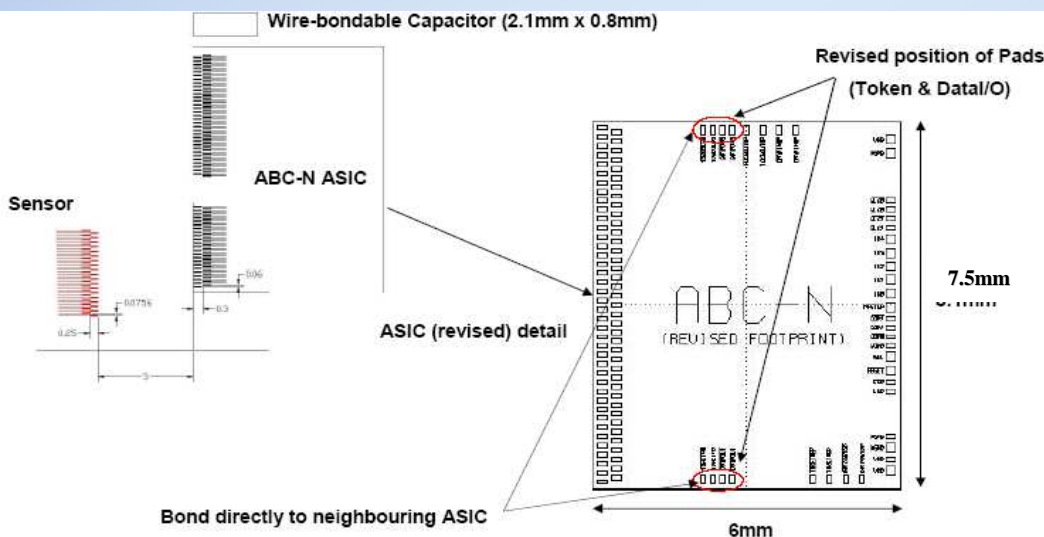
# New Hybrid Designs

- Multi-layer kapton high density circuit on high thermal conductivity (carbon-carbon) baseboard
- FE ASIC microchip interconnect and high speed data transmission
- Redundancy scheme designed to allow single FE chip failure without loss of read-out from neighbouring ASICs

- 2 “fingers” per hybrid populated with 2 columns of ABC-Ns (20 ASICs per finger, 40 ASICs total)
- Chip-to-chip “direct” token and data passing added
- Provisional Redundancy scheme implemented on the hybrid
- Hybrid is electrically one object
- 4 Layer Kapton (conservative design)
- No tracking under ASIC front-end
- 2 Layers for routing and 2 for Power/Gnd planes
- 100um Track & Gap
- 350um Vias
- DCS, Module Power management, CLK/COM and Data buffering may require one or two(?) additional Module Controller ASICs per hybrid.

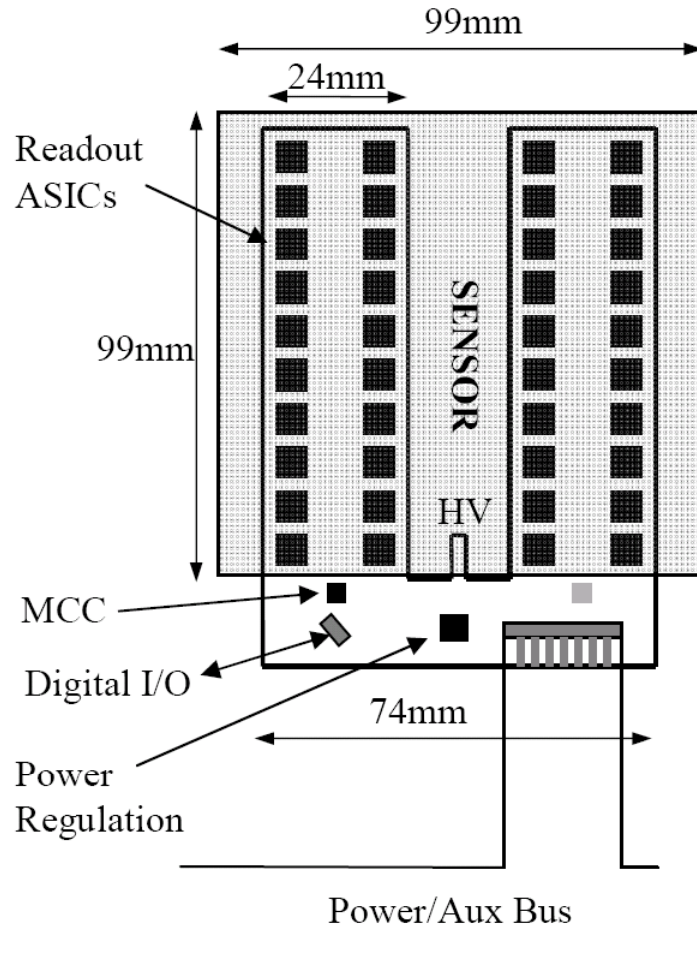
**A. Greenall**

Tentatively, a hybrid could look like:





# Review of Hybrid concept



## Detail

- Designed to match to a single sensor of 99mm x 99mm
- 2 'fingers' per hybrid populated with 2 columns of 10 ABCNs (40 total)
- 4 Cu Layers with Kapton dielectrics
- Standard build (to maximise yield)
  - 100 $\mu$ m track and gap
- Wire bonding directly from ABCN to sensor
  - Eliminates the need for pitch adaptors
  - ABCN die size is fixed to 7.5mm width to allow this
  - Length is still unknown (currently 8.2mm)

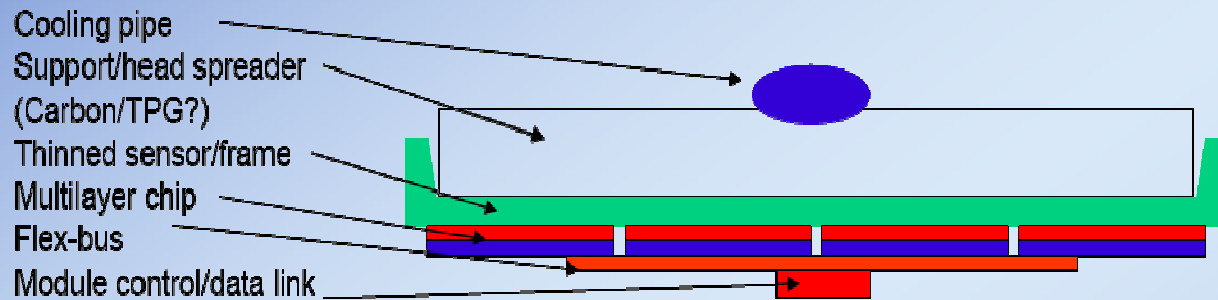
**A. Greenall**

MCC: Module Controller Chip

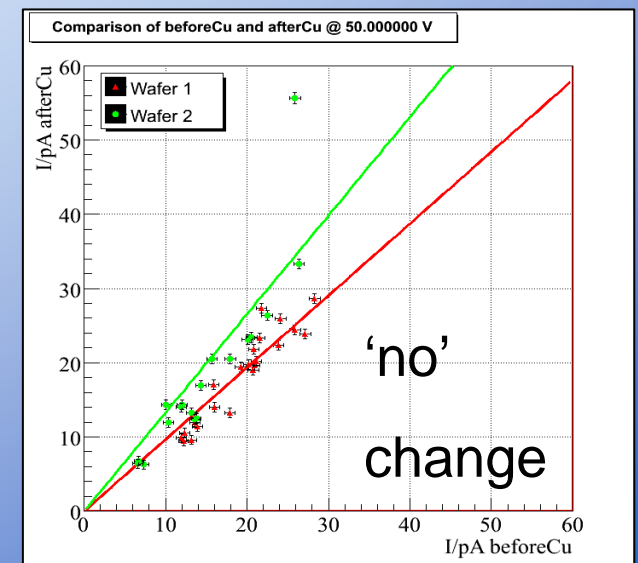
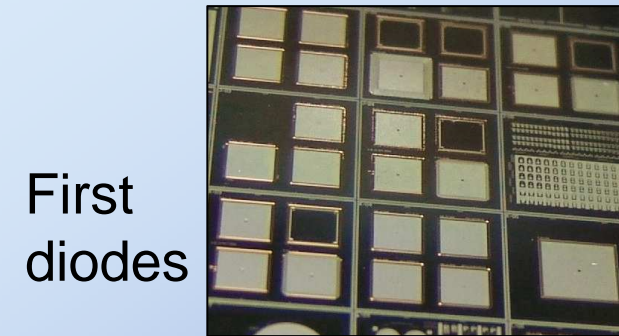
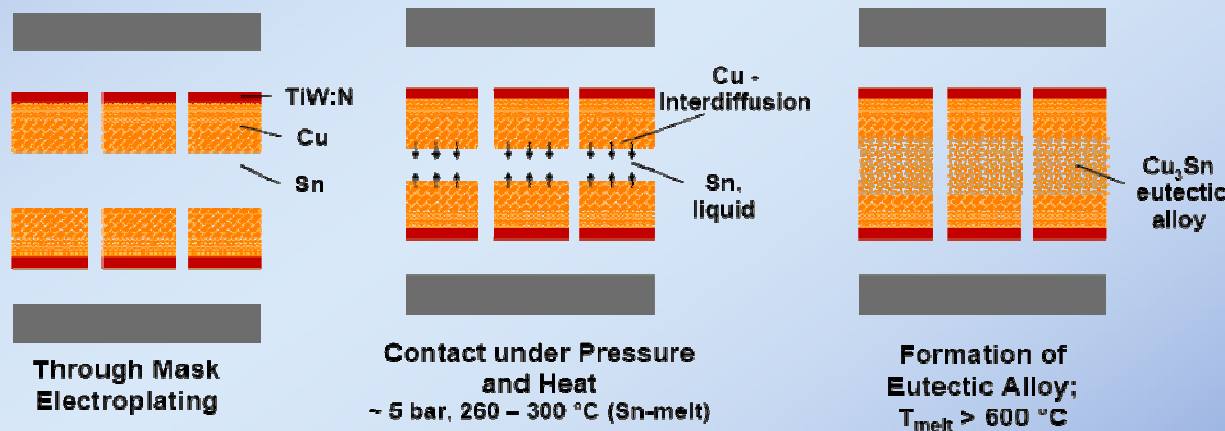
# HEP R&D on Vertical (3D) Integration

- Work already underway in Germany and US
- UK has purchased RD50 wafers for trials adding polyimide layers to Micron sensors
- Survey of companies for MCMD in progress

- 1) Low  $I_{leak}$ , low  $V_{dep}$
- 2) Large live-fraction
- 3) SLID interconnection
- 4) 3D integration



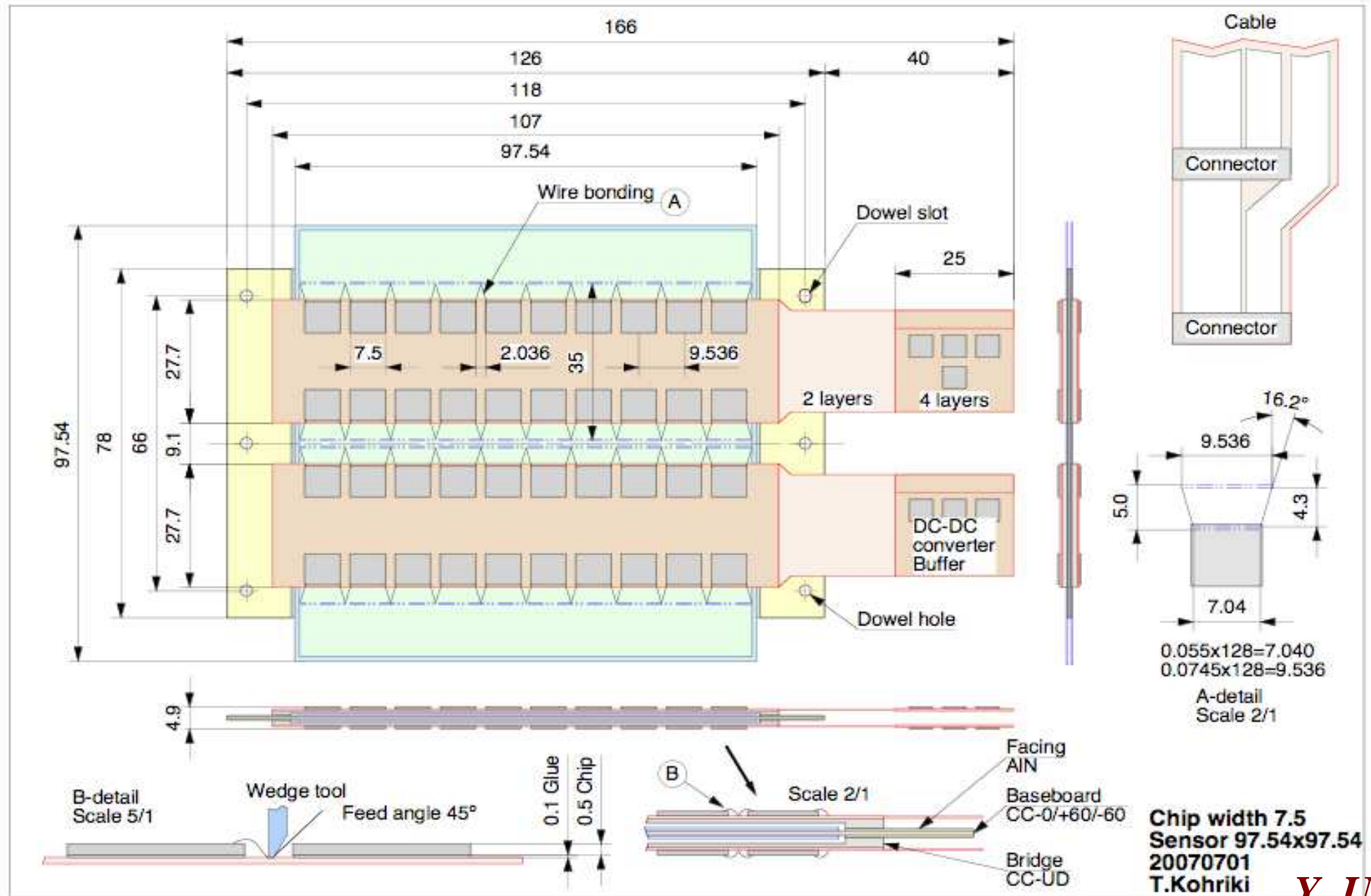
## Solid Liquid Interdiffusion (SLID), IZM Munich



Conducted by: Bonn, Dortmund, MPI, Oslo, Interon, IZM

# Double-sided Hybrid Designs - KEK

Four hybrids/module, four connectors/module square sensors (9.754 cm x 9.754 cm)



# SLHC module - Optimization

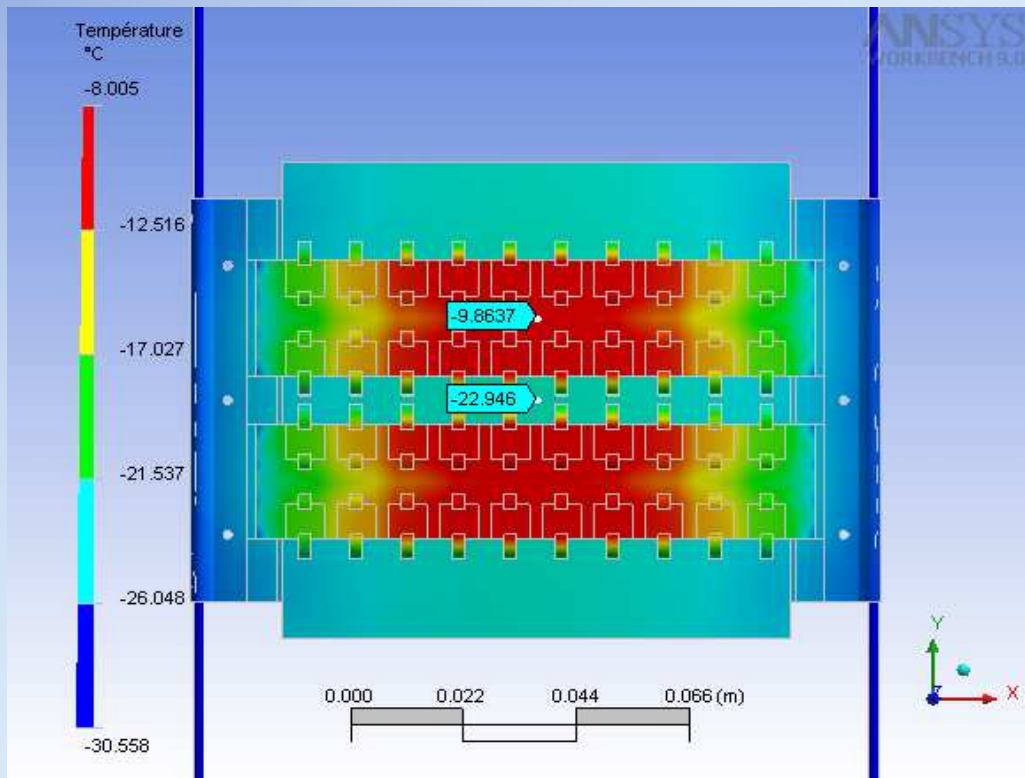
FEA thermal analyses using ANSYS

**Need cooling from both ends (current ATLAS single-ended cooling)**  
(2-dimensional calculation)

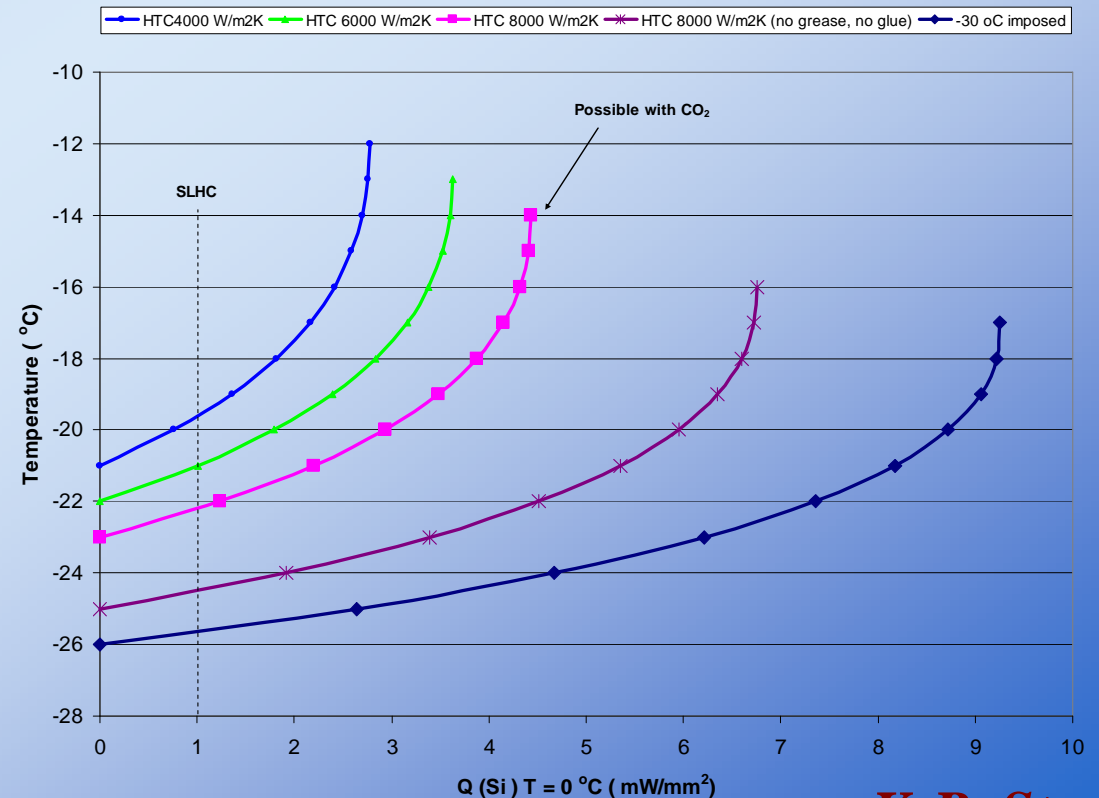
- 0.1mm thick thermal grease around cooling pipe (2W/m/K)
- Dead air between sensor and hybrid (0.024W/m/K)

## Thermal distribution

2mW/ch, HTC 8000 W/m<sup>2</sup>K, -30 °C,  $Q(\text{Si}) = 0$

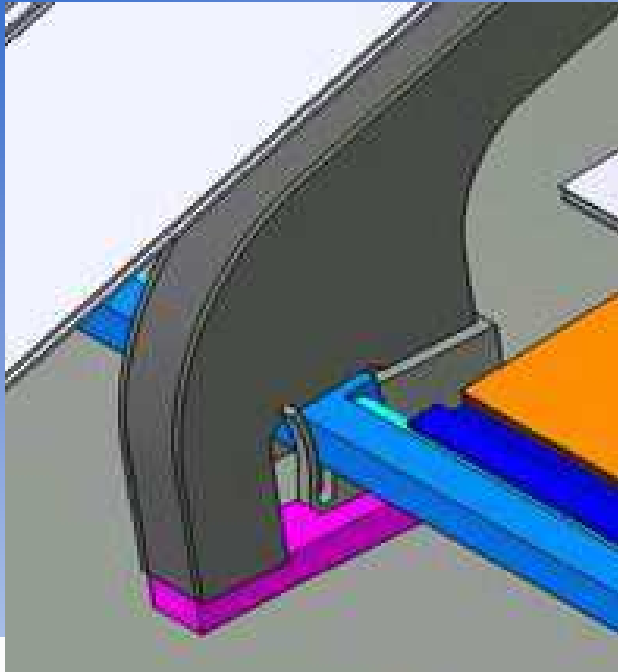


## Runaway simulations for different cooling systems (cooling -30 °C , 2mW/ch)

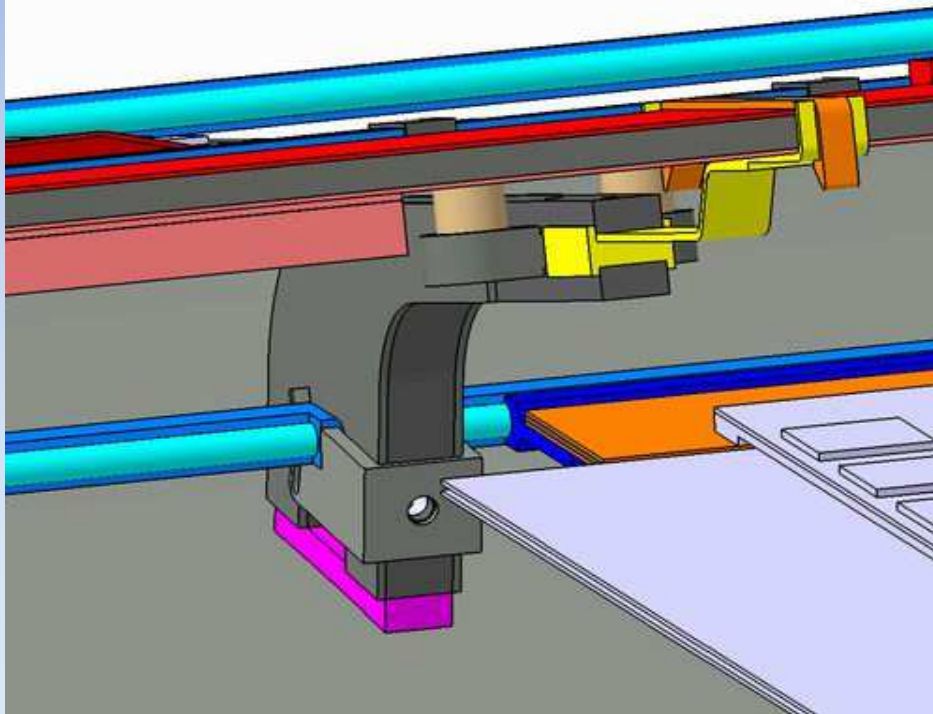


# Individual Module - Direct Mounting

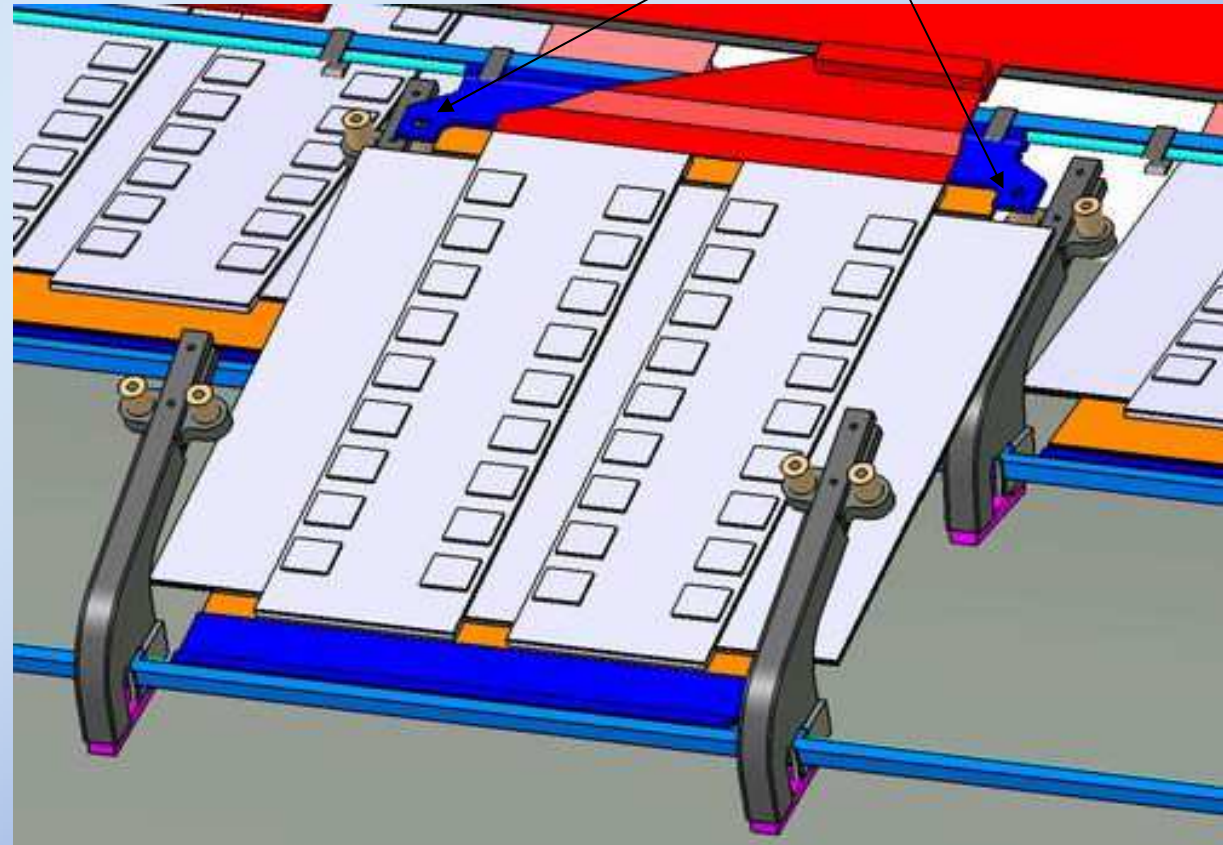
- 3rd “point” is defined by the pipe
- Cooling block is set with 2 fixation points on the pig-tail side
- 1 bracket is holding 2 neighboring modules
- The bottom left pipe is embedded in the brackets and must be assembled before the module.



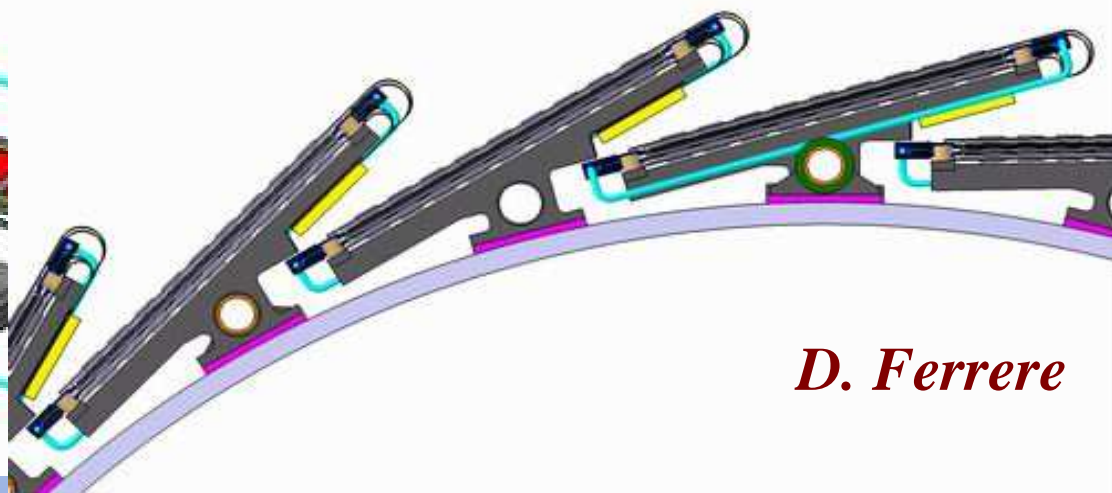
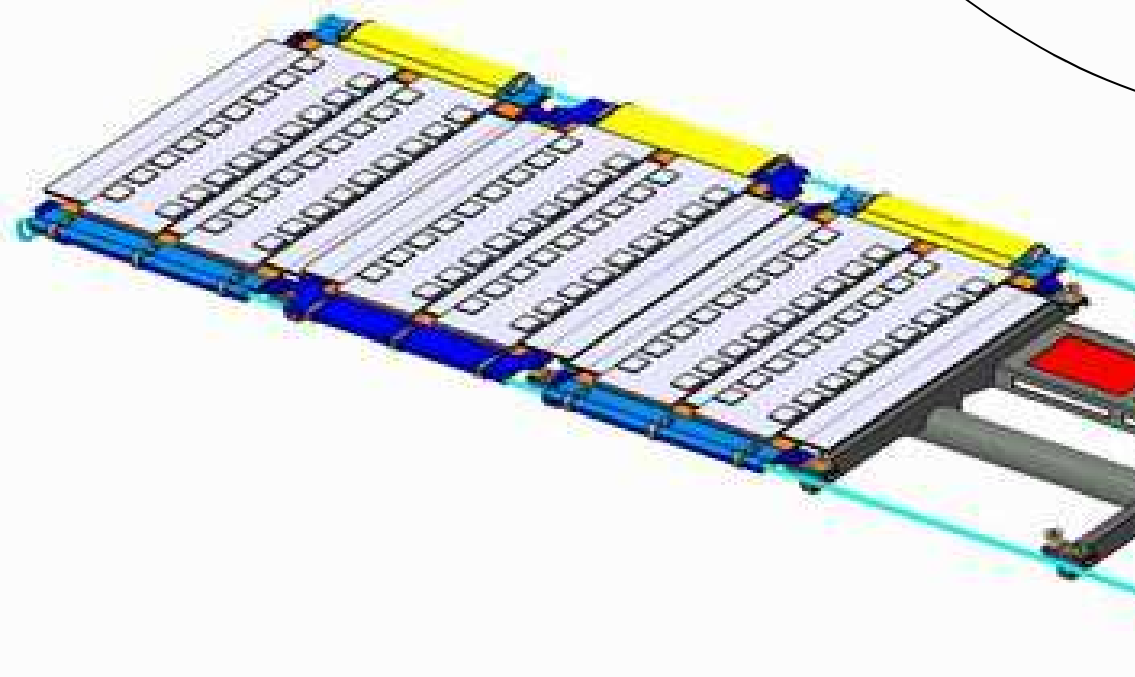
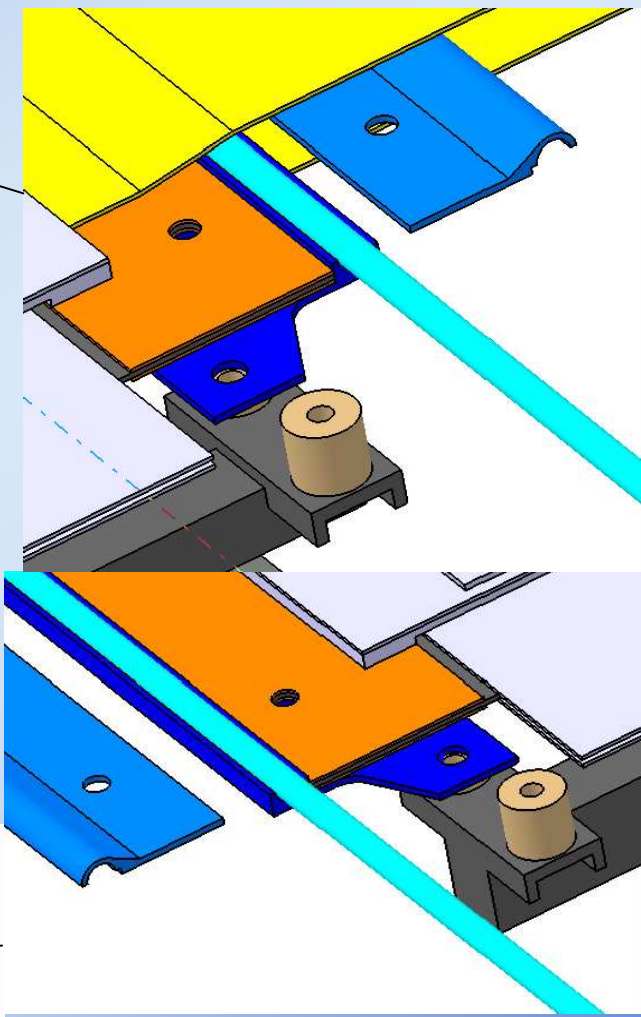
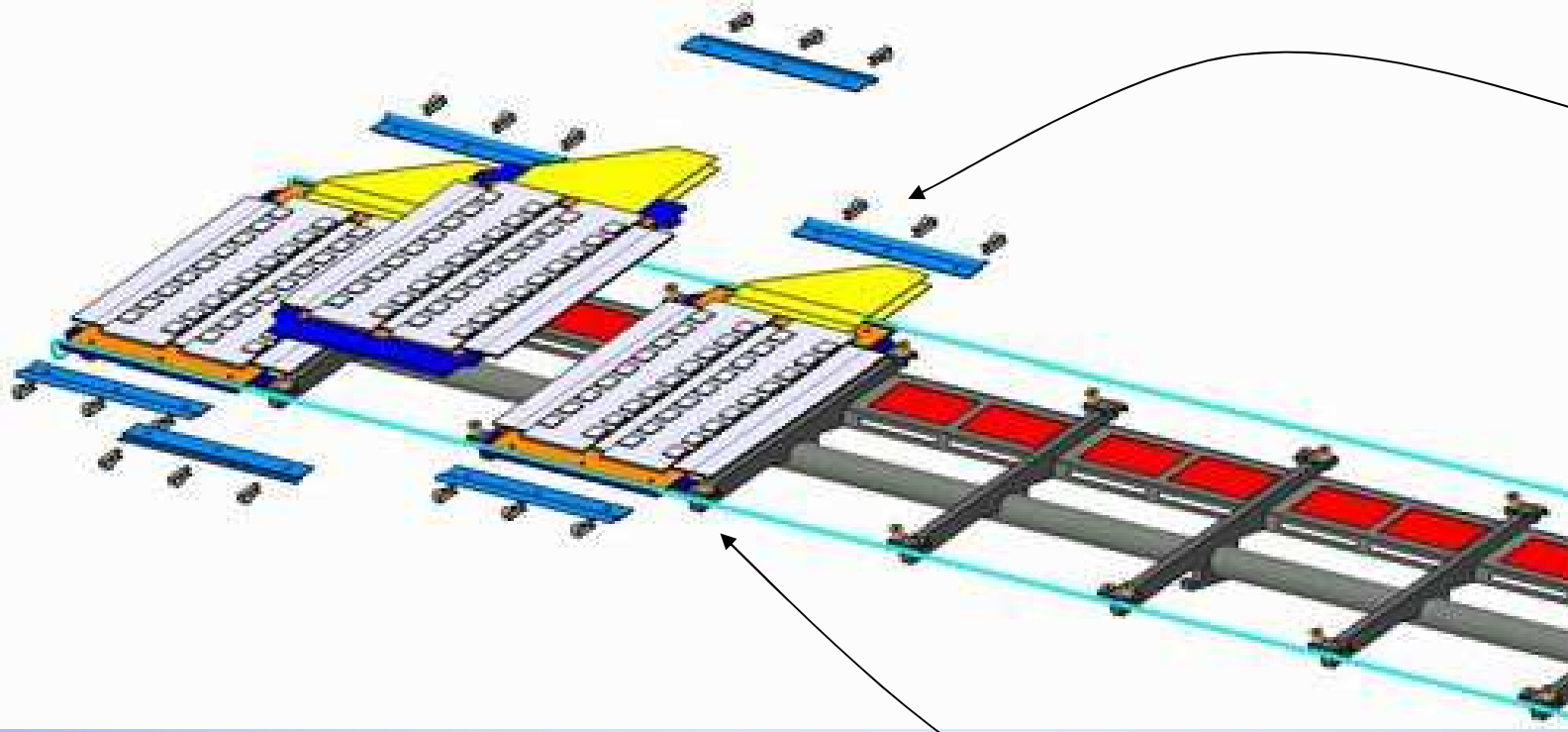
*Y. Unno*



**2 fixed mounting points**

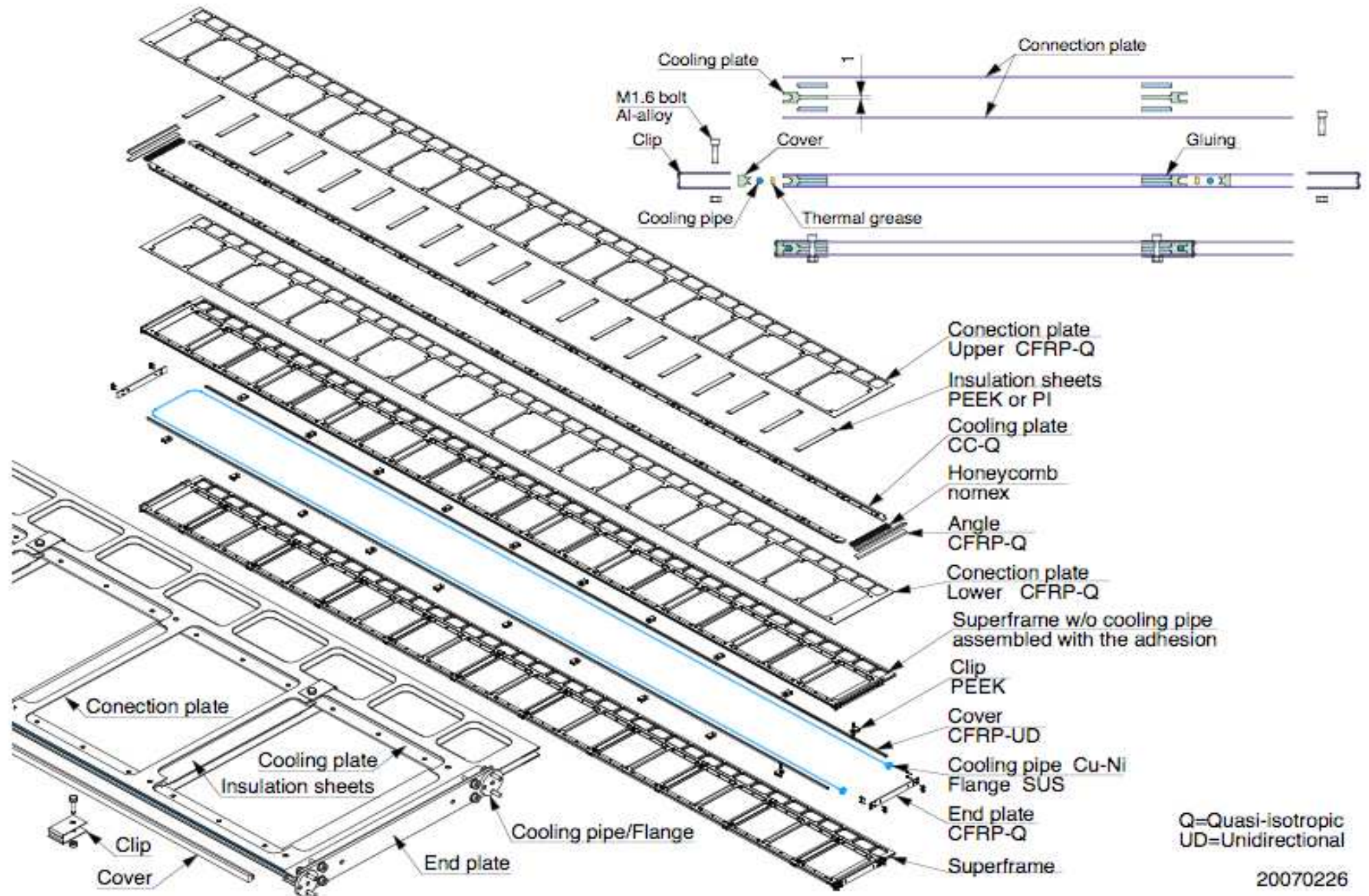


# Integrated Bracket Support Structure

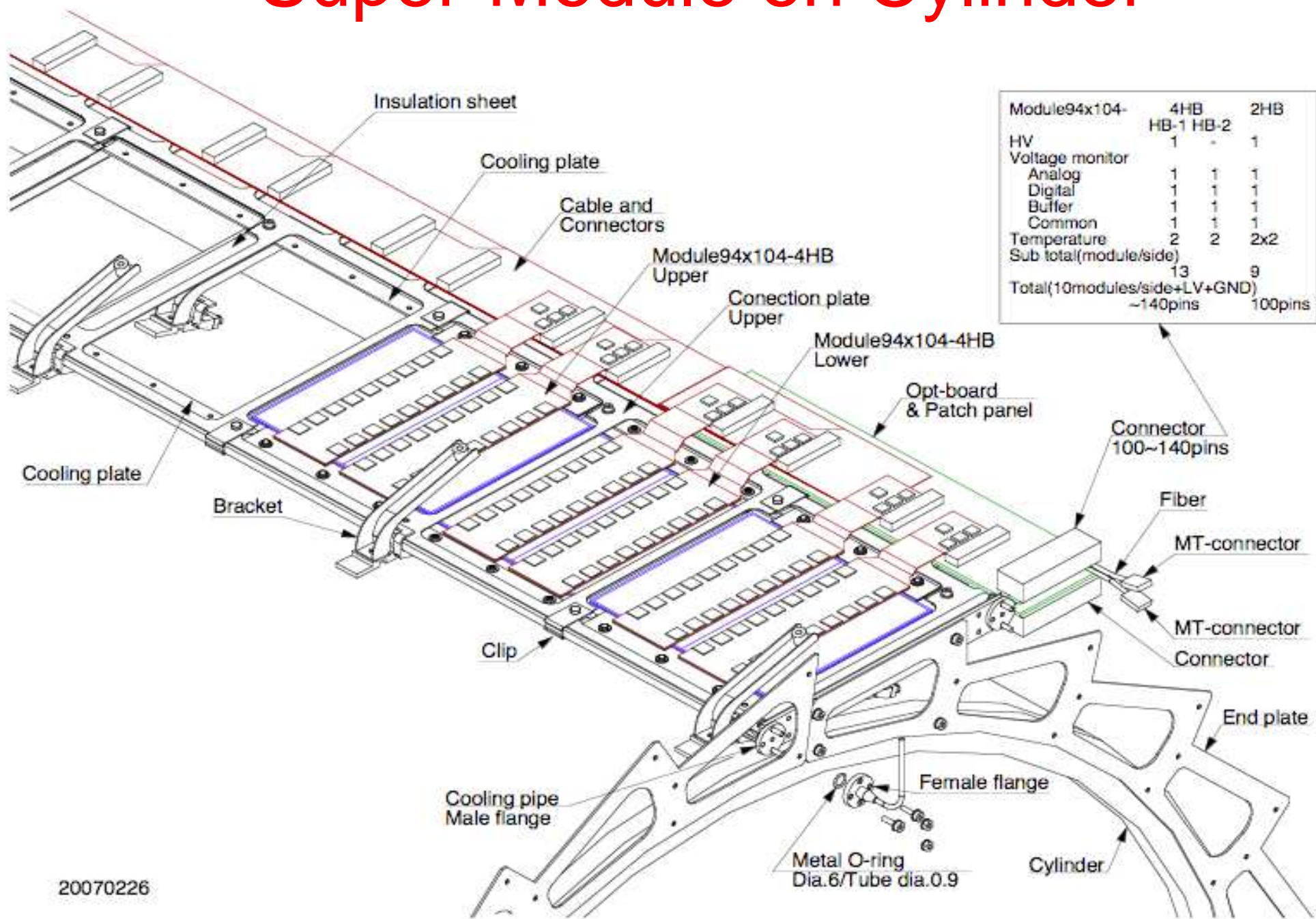


*D. Ferrere*

# Super-Module Concepts: Super-Frame



# Super-Module on Cylinder



20070226



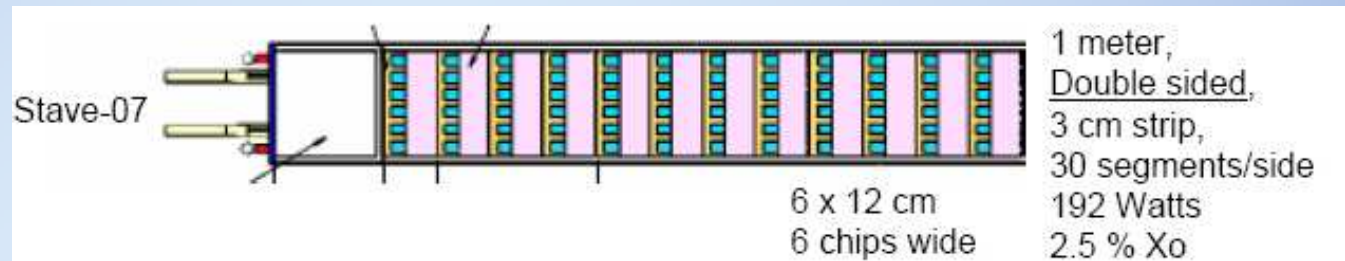
# Stave Module Concept

- The “stave” concept has hybrids glued to sensors glued to cold support
- A first prototype version based on the CDF run-IIb concept but using



ATLAS ASICs already exists

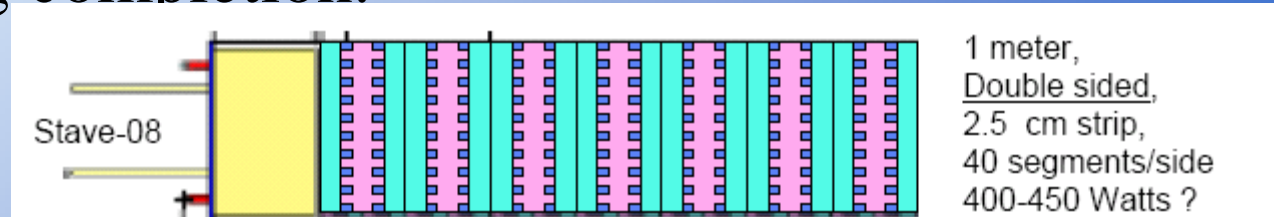
- A 6-chip wide version (Stave 2007) will use short p-in-n sensors and incorporate many of the final proposed, mechanical, thermal, electrical, serial powering and read-out features.



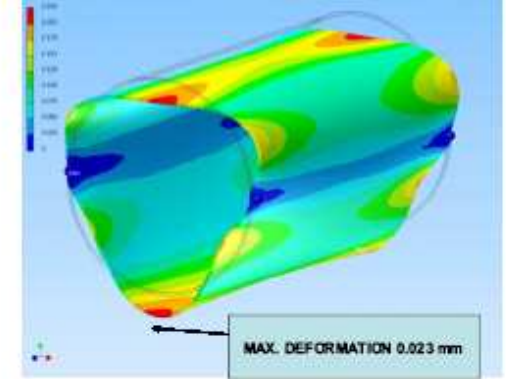
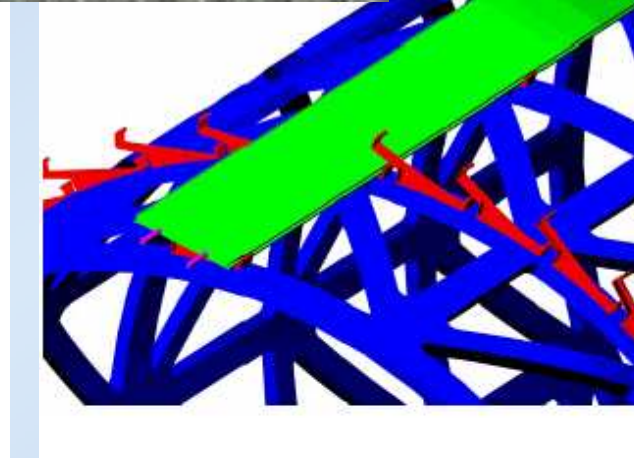
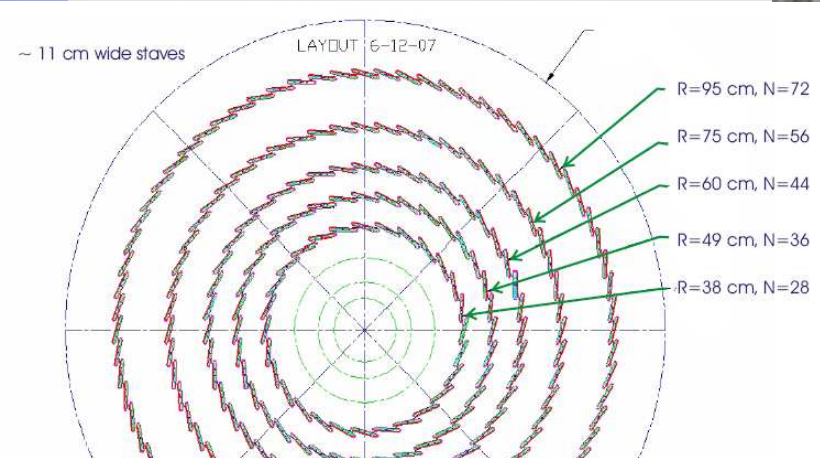
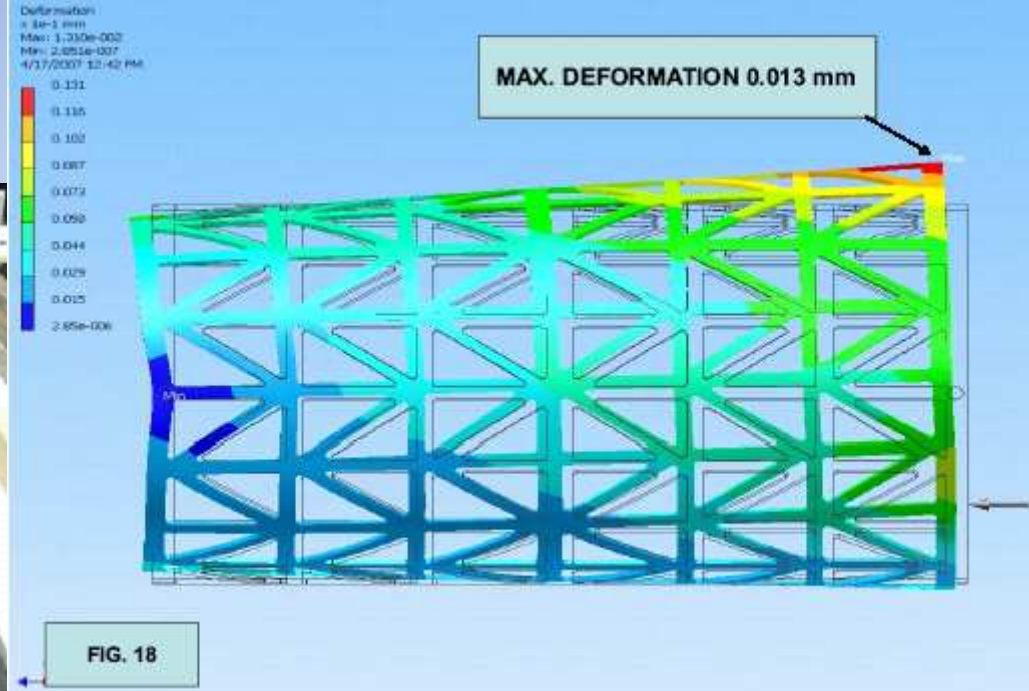
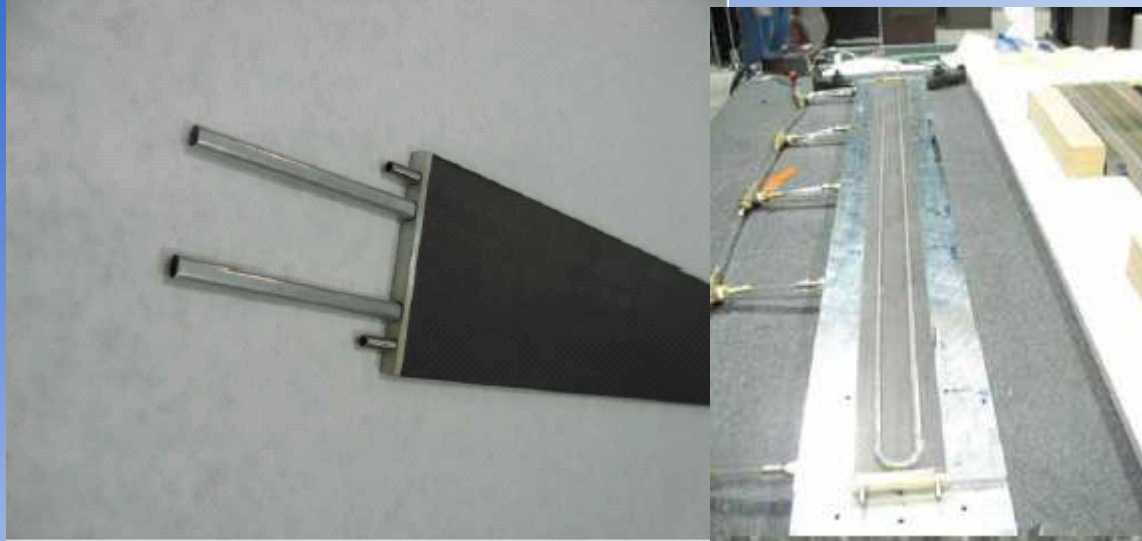
- The first prototype staves are expected by Autumn this year
- Stave core fabrication, BeO hybrid design, cooling concepts and automated assembly nearing completion.

*C. Haber*

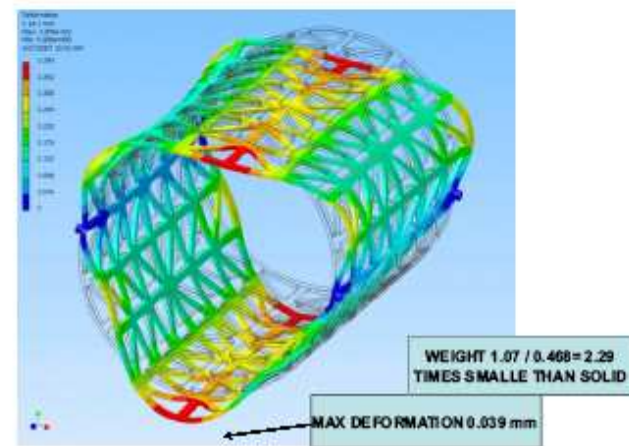
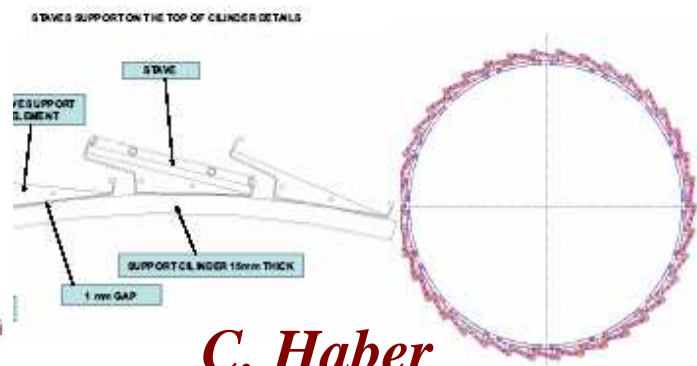
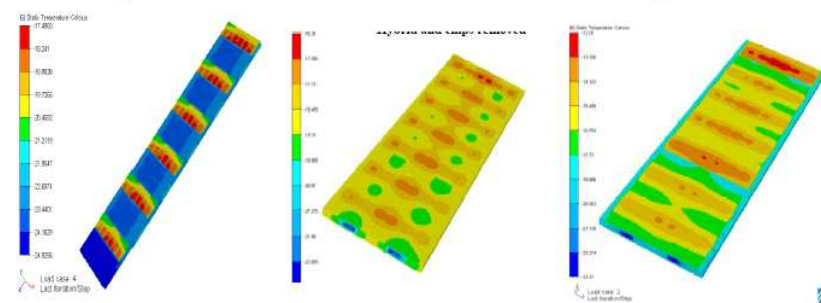
- 10 chip wide version under development



# Stave R&D



Single sided      DS low cable TC      DS high cable TC

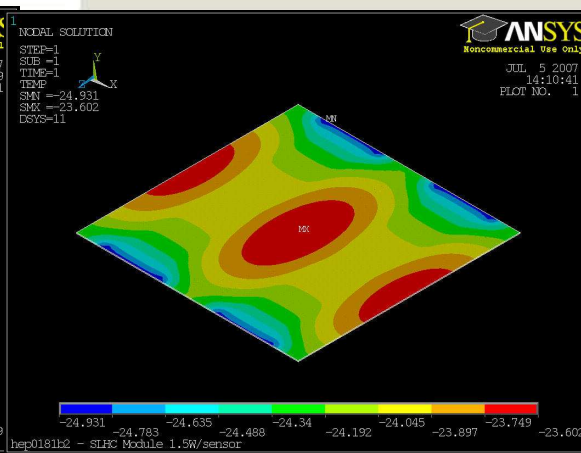
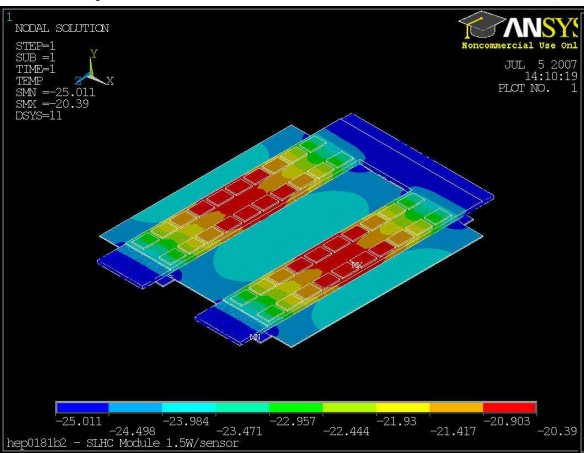
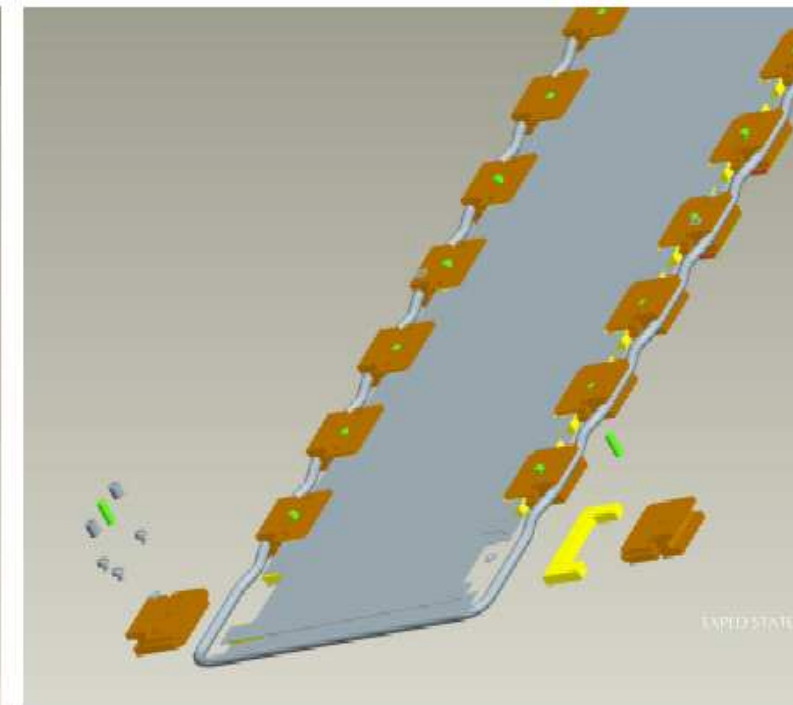
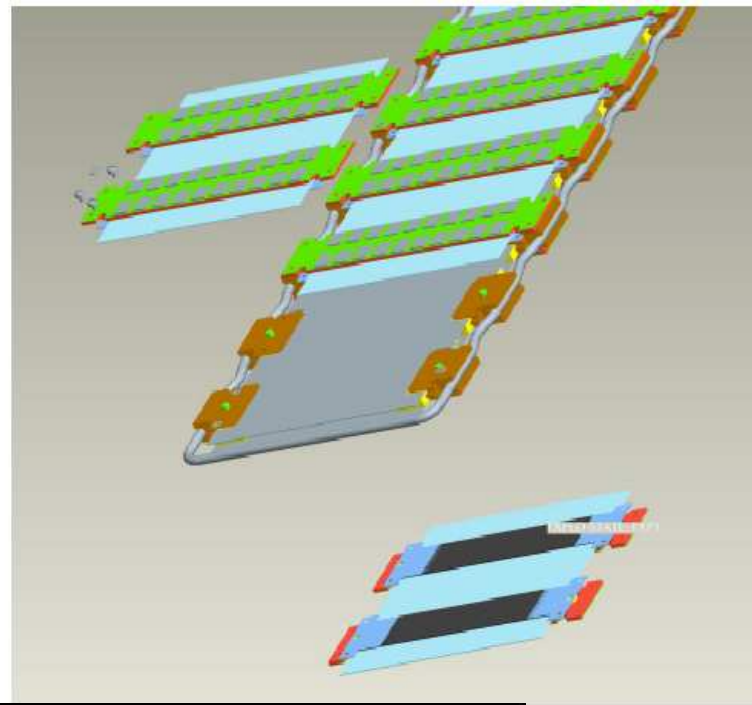


*C. Haber*

# Single-sided Concept

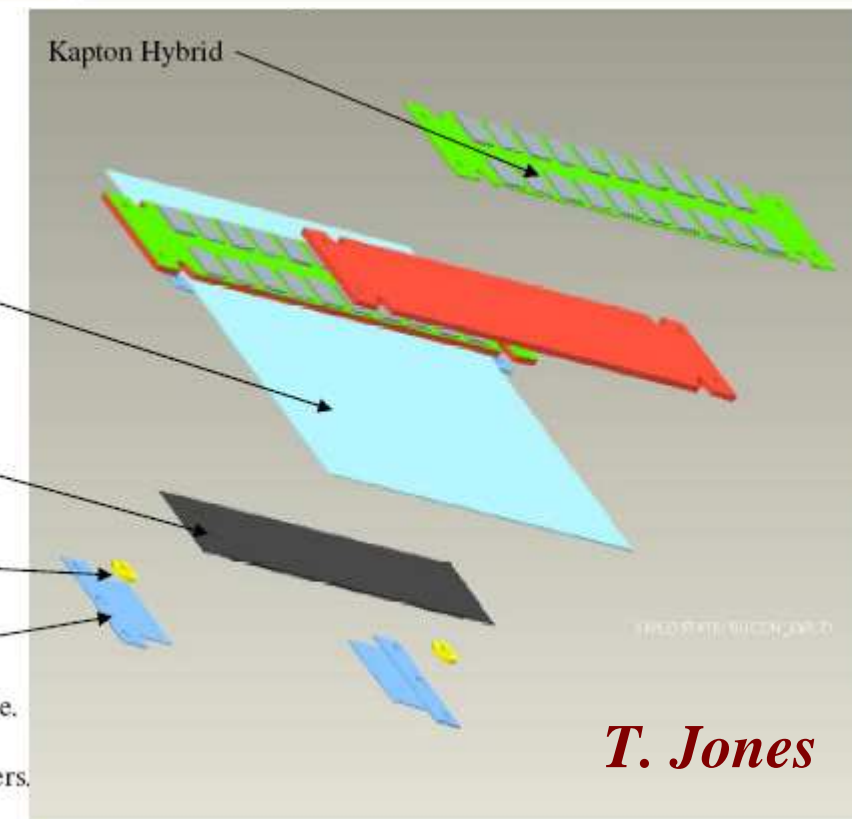
## Bridged hybrid assemblies on cooled support

1.5W/Sensor  
 Max Chip temp: -20.4C  
 Max Silicon Temp: -23.6C  
 Temp Gradient over Si: 1.33C



## Possible Demountable Module/Stave Concept (single-sided assembly step)

- Single sided silicon module.
- Alumina and TPG heat spreader, spliced as in ATLAS module.
- Integral precision location washers (holes and slots)
- Carbon Carbon hybrid base, with added non conductive spacers.

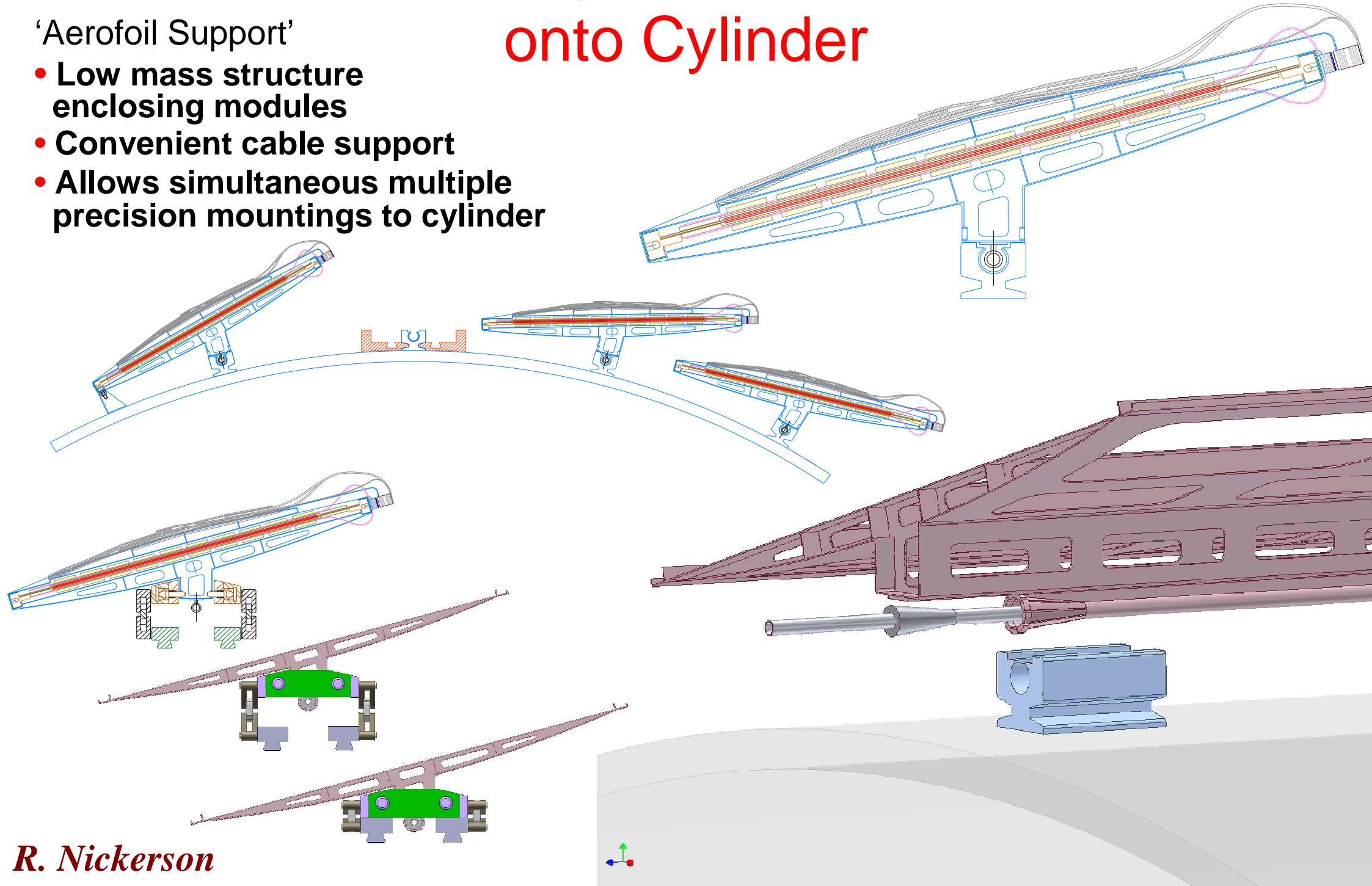


*T. Jones*

# Alternative Mounting Scheme for Super-Module onto Cylinder

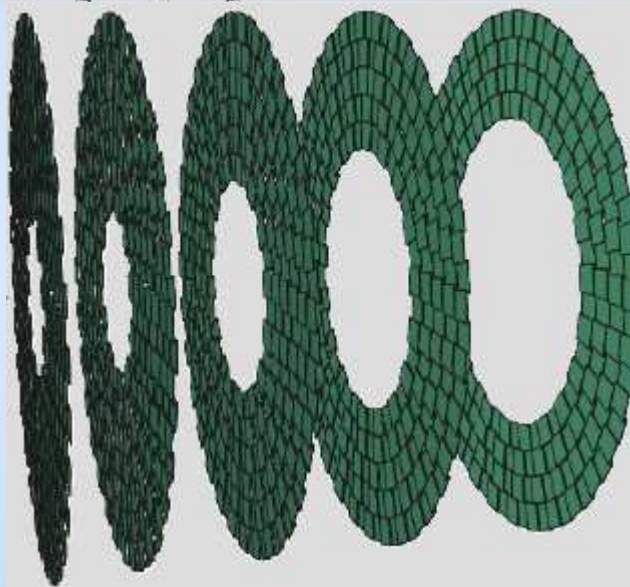
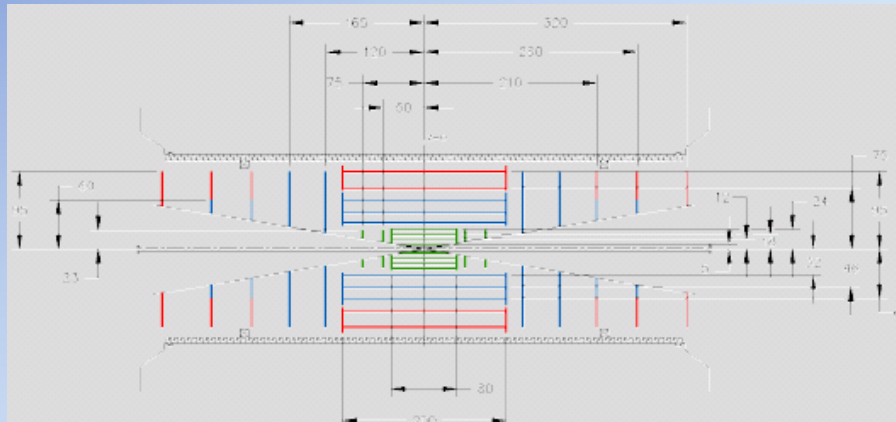
'Aerofoil Support'

- Low mass structure enclosing modules
- Convenient cable support
- Allows simultaneous multiple precision mountings to cylinder



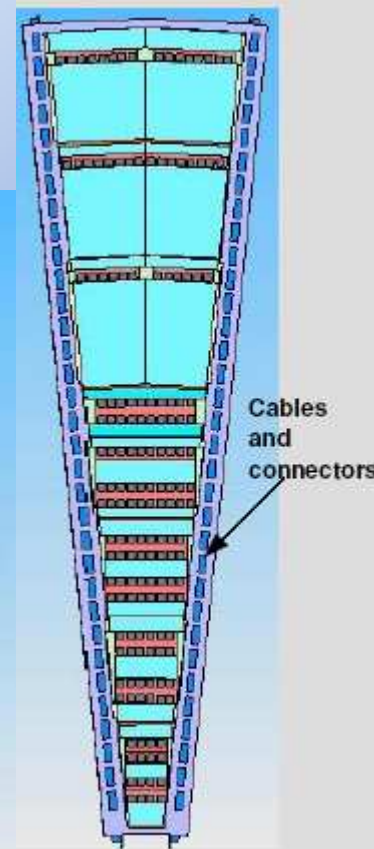
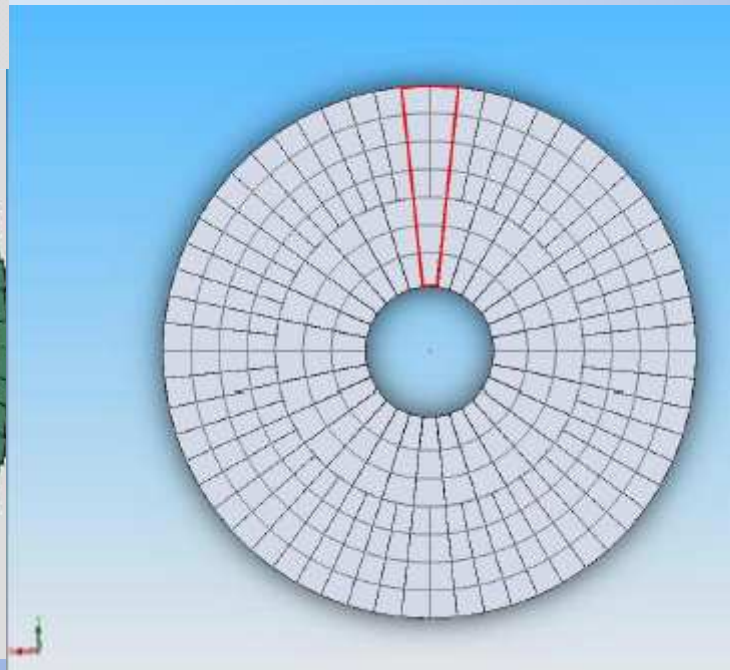
# Forward Module Concepts

- As for current ATLAS SCT, Forward Modules likely to require several different wedge shaped sensors
- 5 discs on each side with outer radius 95cm and inner radii from 30cm



Mean pitch  
about  $80\mu\text{m}$   
as at present

Can consider super-modules/staves  
or individual modules as now



# Detectors for sLHC

**G. Casse**

**University of Liverpool Group**

**6<sup>th</sup> December 2007**

- **Proposed Tracker Layout and Simulations  
(Radiation and Occupancy)**
- **Sensor and FE Electronics R&D**
- **Microstrip Module and Engineering Concepts**
- **Power, DCS, Opto-electronics, Services, Cooling, ...**
- **Conclusions**

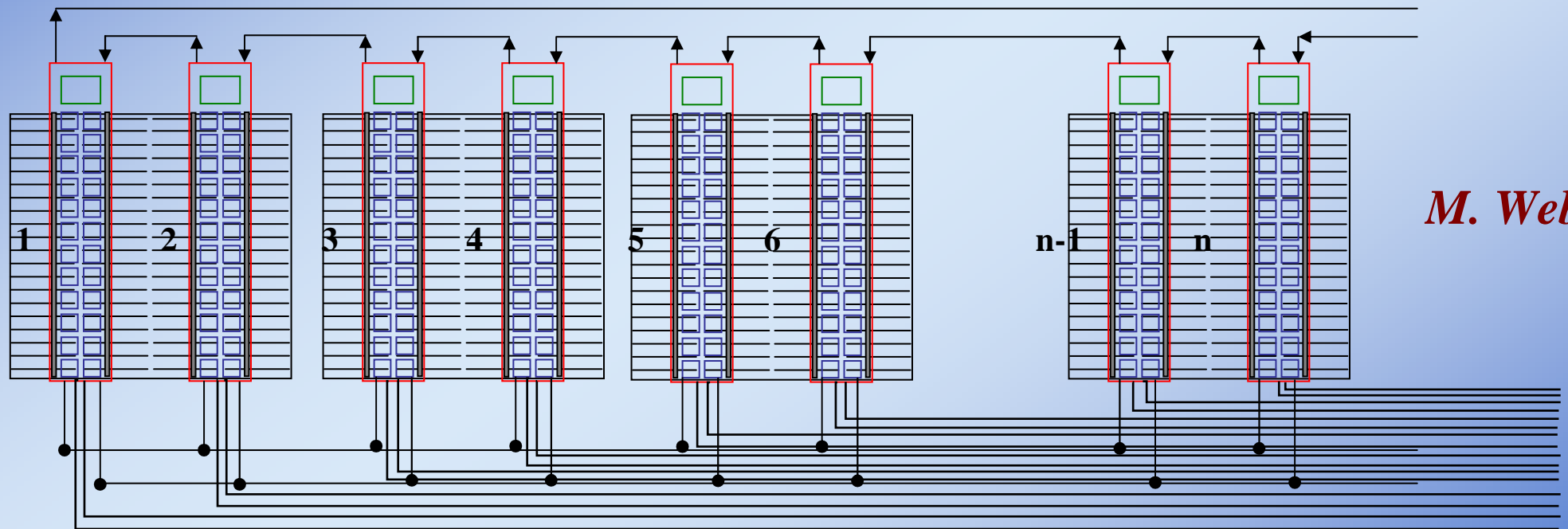
# Powering Issues

$V_{ABC-N} = 2.5 \text{ V}$ ;  $I_{Hybrid} = 2.4 \text{ A}$ ; 20 hybrids. **Low V + High I  $\rightarrow$   $I^2R$  losses in cables**  
(Want power transmission at High V + Low I)

**Serial Powering:**  $n=20$ ;  $I_H = I_{PS} = 2.4 \text{ A}$ ;  $V_{PS} = nV_{ABC-N} = 50 \text{ V}$

Also saves factor  $\sim 8$  in power cables/length over SCT

- Need detailed studies of failure modes and recovery



*M. Weber*

**DC-DC Conversion :**  $n=20$ ;  $g=20$ ;  $I_{PS} = n/g I_H = 2.4 \text{ A}$ ;  $V_{PS} = gV_{ABC-N} = 50 \text{ V}$

Parallel powering also saves factor  $\sim 8$  in power cables as for Serial Powering

- Issues with switched capacitors (noise?) and need for custom design to get large  $g$   
(Independent powering with DC-DC costs too many cables)

# Total Microstrip Power

	BIS	BOS	ECA	ECB	Total
Power [kW]	71.8	45.7	18.3	18.3	154.2
	47%	30%	12%	12%	

- Going to  $P_{\text{chan}} = 2\text{mW} \rightarrow P_{\text{total}} = 120\text{kW}$ ,
- Several contributions missing (SMC, Opto-converter, DCS, etc...)
- Best guess (strips)  $P_{\text{total}} = 150\text{kW}$  within  $\pm 40\text{kW}$  (2-3xSCT).
- Dominated by barrel (even if BOS shortened).
- Investigating cooling using  $\text{C}_3\text{F}_8$  (again),  $\text{C}_2\text{F}_6$  or  $\text{CO}_2$
- Reuse of existing services could represent a major challenge



# DCS: SLHC- Services

# of rows (draft) - SLHC Strawman Layers for barrel:

Layer	# of rows	Radius (mm)
SS layer 1	28	380
SS layer 2	36	490
SS layer 3	44	600
LS layer 1	56	750
LS layer 2	72	950

Numbers not yet available for the ECs

Estimation of 2 interlock temperature sensors per cooling loop → 944 NTCs in total

SCT barrel DCS: 48 type 2-DCS cables of (28 pins Milli-Grid) → 672 twisted pairs!

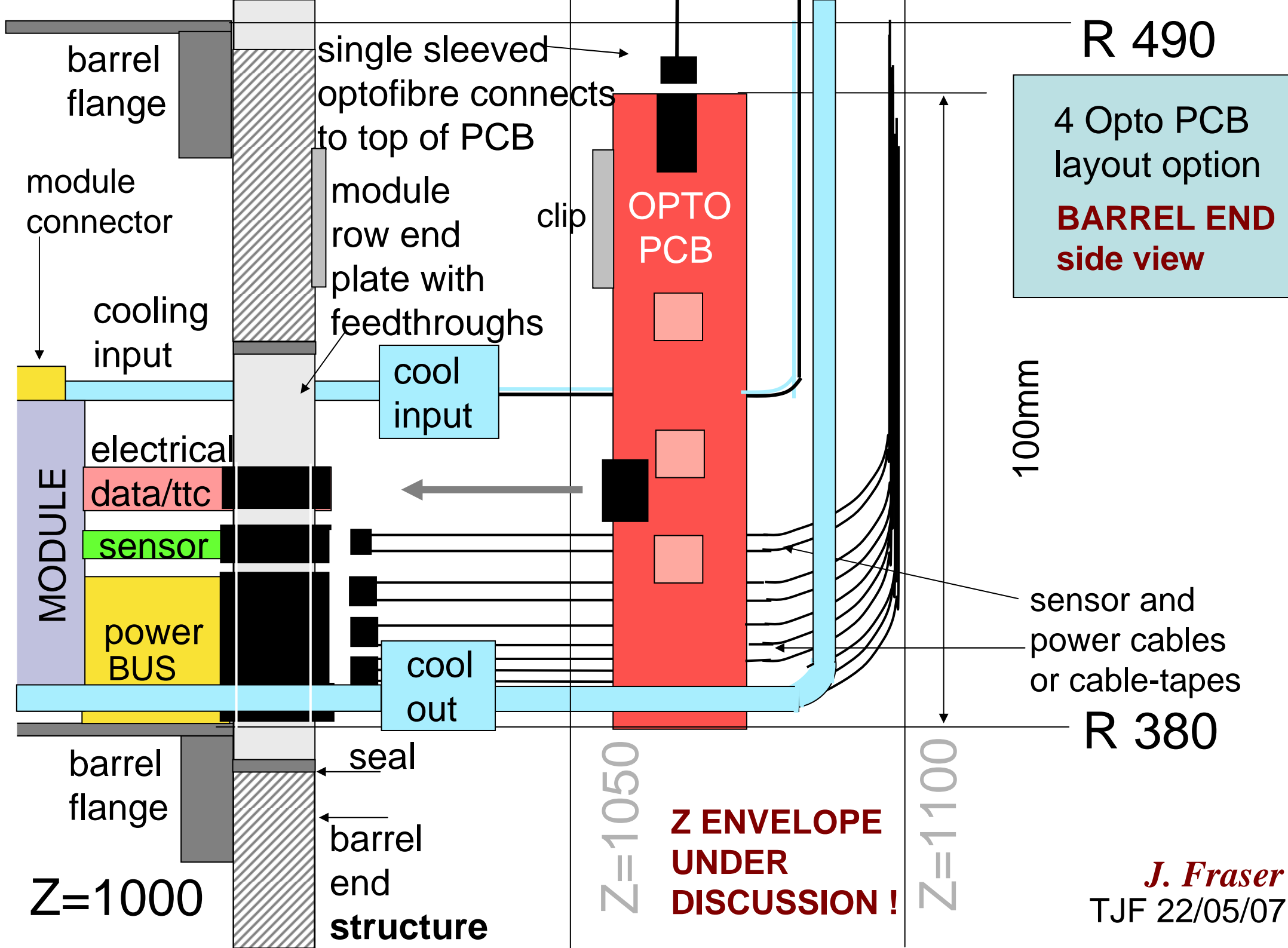
SCT ECs DCS: 80 type 2-DCS cables of (28 pins Milli-Grid) → 1120 twisted pairs!

Barrel SS layers could use the current barrel DCS type 2 for the interlock  
& LS could use part of the current EC DCS type 2.  
→ Most probably NOT enough left for the SLHC ECs

**Can existing cables be used?**

**What type of connectors required and where?**

*D. Ferrere*



R 490

4 Opto PCB layout option  
**BARREL END side view**

100mm

sensor and power cables or cable-tapes

R 380

Z=1050

**Z ENVELOPE UNDER DISCUSSION !**

Z=1100

barrel flange

module connector

cooling input

MODULE  
 electrical  
 data/ttc  
 sensor  
 power BUS

single sleeved optofibre connects to top of PCB

module row end plate with feedthroughs

clip

OPTO PCB

cool input

cool out

barrel flange

seal

barrel end structure

Z=1000

*J. Fraser*

TJF 22/05/07

# Conclusions

- Activities in many areas still just starting with emphasis on completion and commissioning of current ATLAS Detector
- Management structure includes Upgrade Steering Group, Upgrade Project Office and 8 working groups in the area of the tracker replacement alone
- Major recent tracker workshops include: Genoa (18/7/05 - 20/8/05), Liverpool (6/12/07- 8/12/07) and Valencia (10/12/07- 12/12/07)
- **Some impressive progress, but still plenty to do and not so much time to do it ...**

ATLAS Inner Detector Technical Design Report now 10 years old  
[http://atlas.web.cern.ch/Atlas/GROUPS/INNER\\_DETECTOR/TDR/tdr.html](http://atlas.web.cern.ch/Atlas/GROUPS/INNER_DETECTOR/TDR/tdr.html)

- For more material of past internal meetings see ATLAS *indico* pages <http://indico.cern.ch/categoryDisplay.py?categId=350>